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Hsieh

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(54) **SUPER-JUNCTION TRENCH MOSFETS WITH CLOSED CELL LAYOUT HAVING SHIELDED GATE**

(2013.01); *H01L 29/0688* (2013.01); *H01L 29/0696* (2013.01); *H01L 29/1095* (2013.01); *H01L 29/41766* (2013.01); *H01L 29/4236* (2013.01); *H01L 29/4916* (2013.01); *H01L 29/7811* (2013.01); *H01L 29/7813* (2013.01); *H01L 29/7827* (2013.01)

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(58) **Field of Classification Search**

CPC . H04L 63/20; H04L 63/0227; H01L 29/7813; H01L 29/66734; H01L 29/7825
See application file for complete search history.

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US 2016/0163789 A1 Jun. 9, 2016

Related U.S. Application Data

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(51) **Int. Cl.**

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H01L 29/423 (2006.01)
H01L 29/10 (2006.01)
H01L 29/49 (2006.01)
H01L 29/417 (2006.01)
H01L 23/535 (2006.01)

(57)

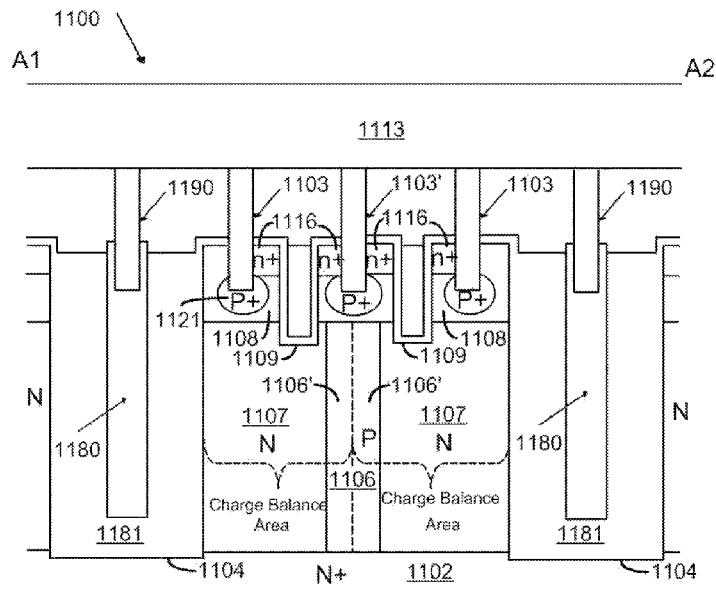
ABSTRACT

A super-junction trench MOSFET with closed cell layout having shielded gate is disclosed, wherein closed gate trenches surrounding a deep trench in each unit cell and the shielded gate disposed in the deep trench. Trenched source-body contacts are at least formed between the closed gate trenches and the deep trench. The deep trench has square, rectangular, circle or hexagon shape.

(52) **U.S. Cl.**

CPC *H01L 29/0634* (2013.01); *H01L 23/535*

8 Claims, 27 Drawing Sheets



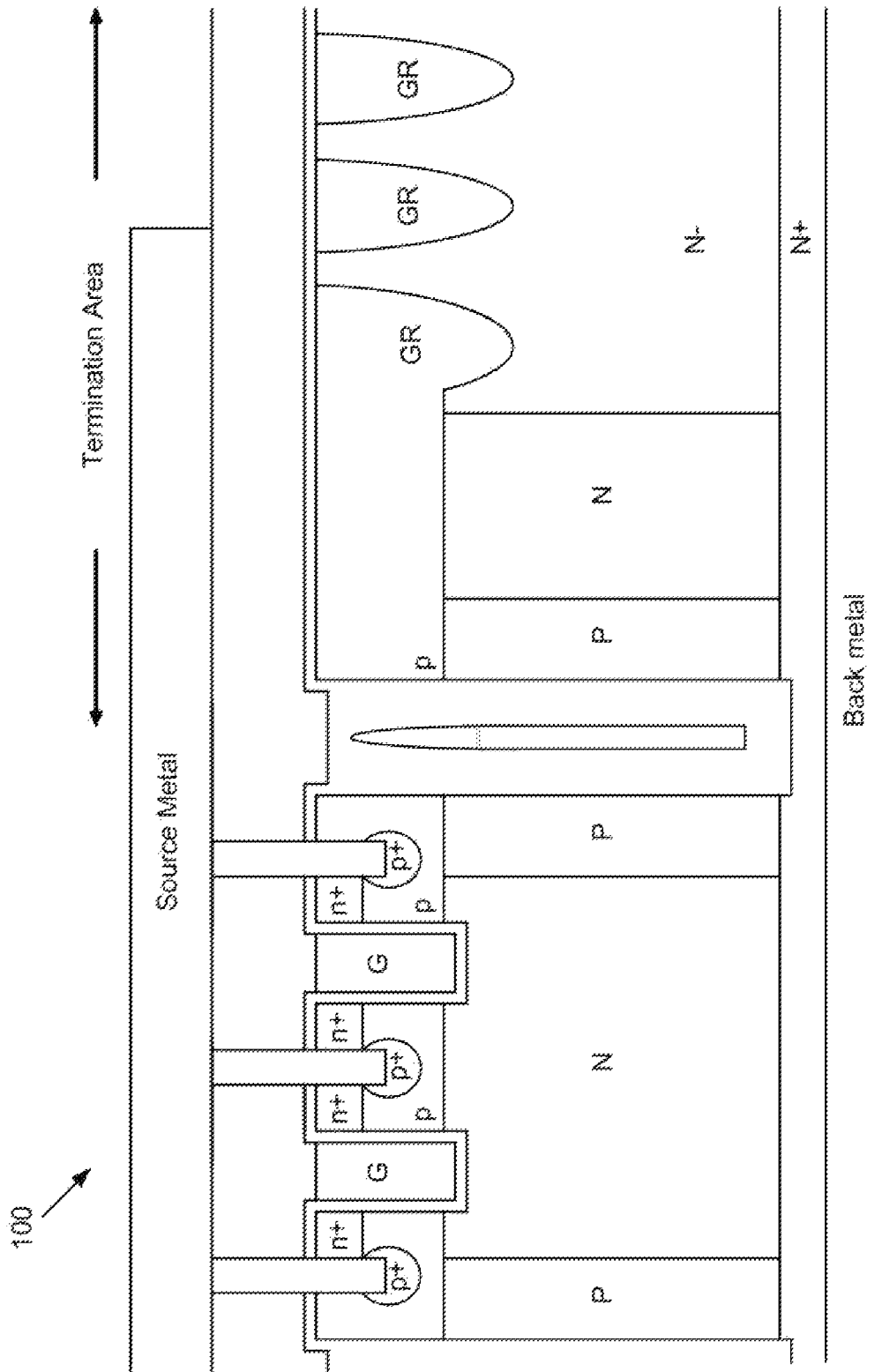


Fig.1 (Prior Art)

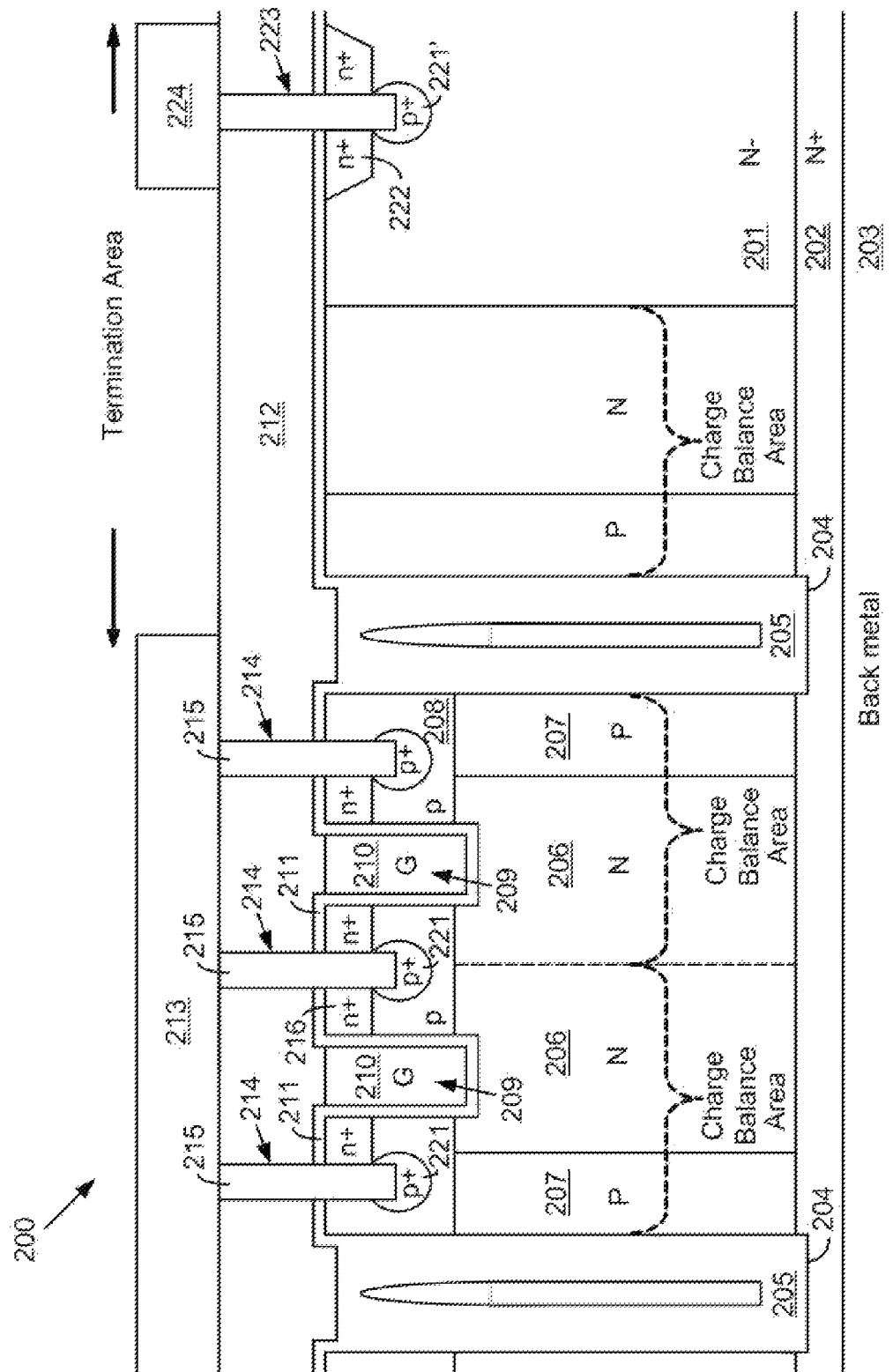


Fig. 2A

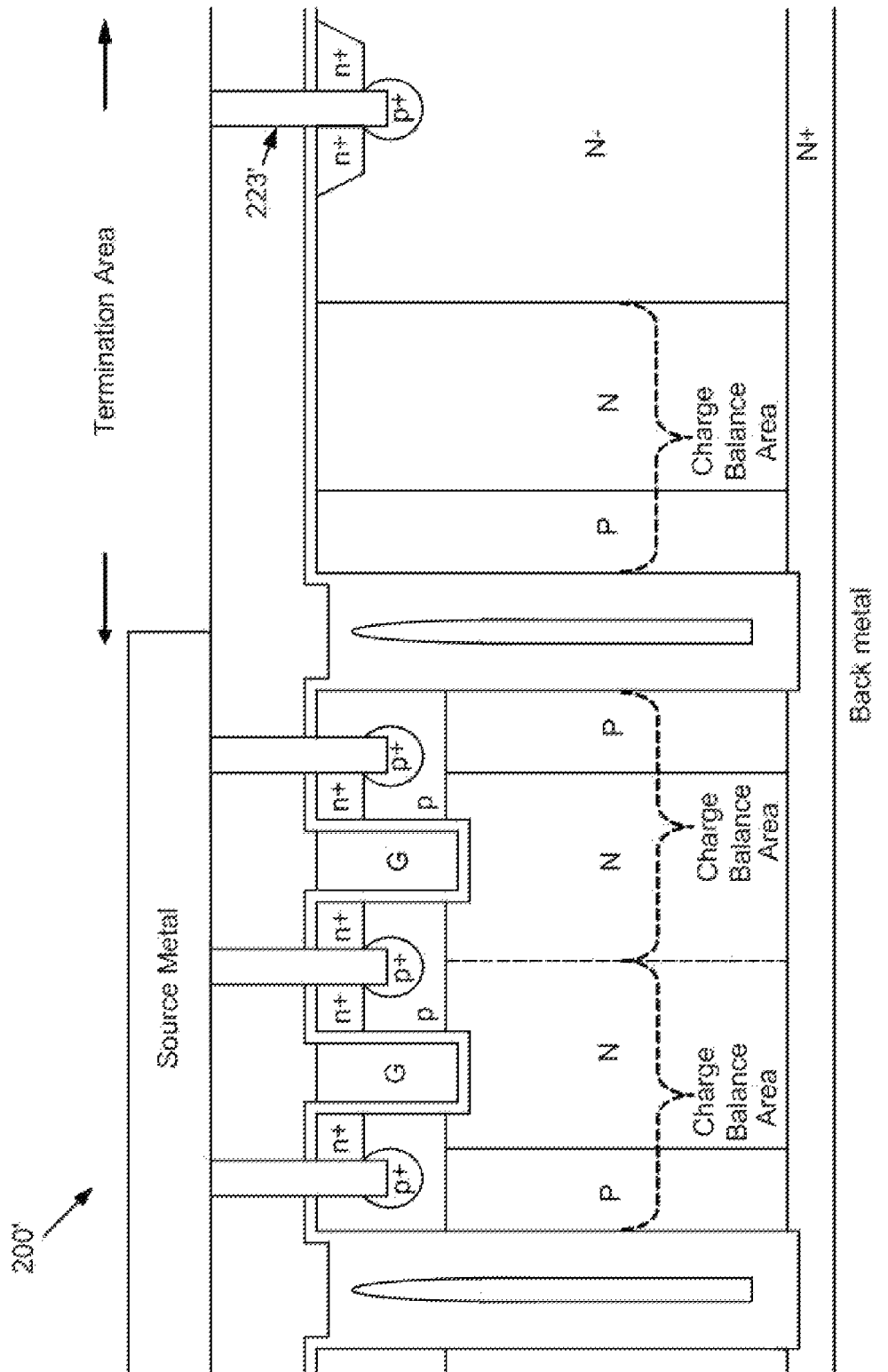


Fig. 2B

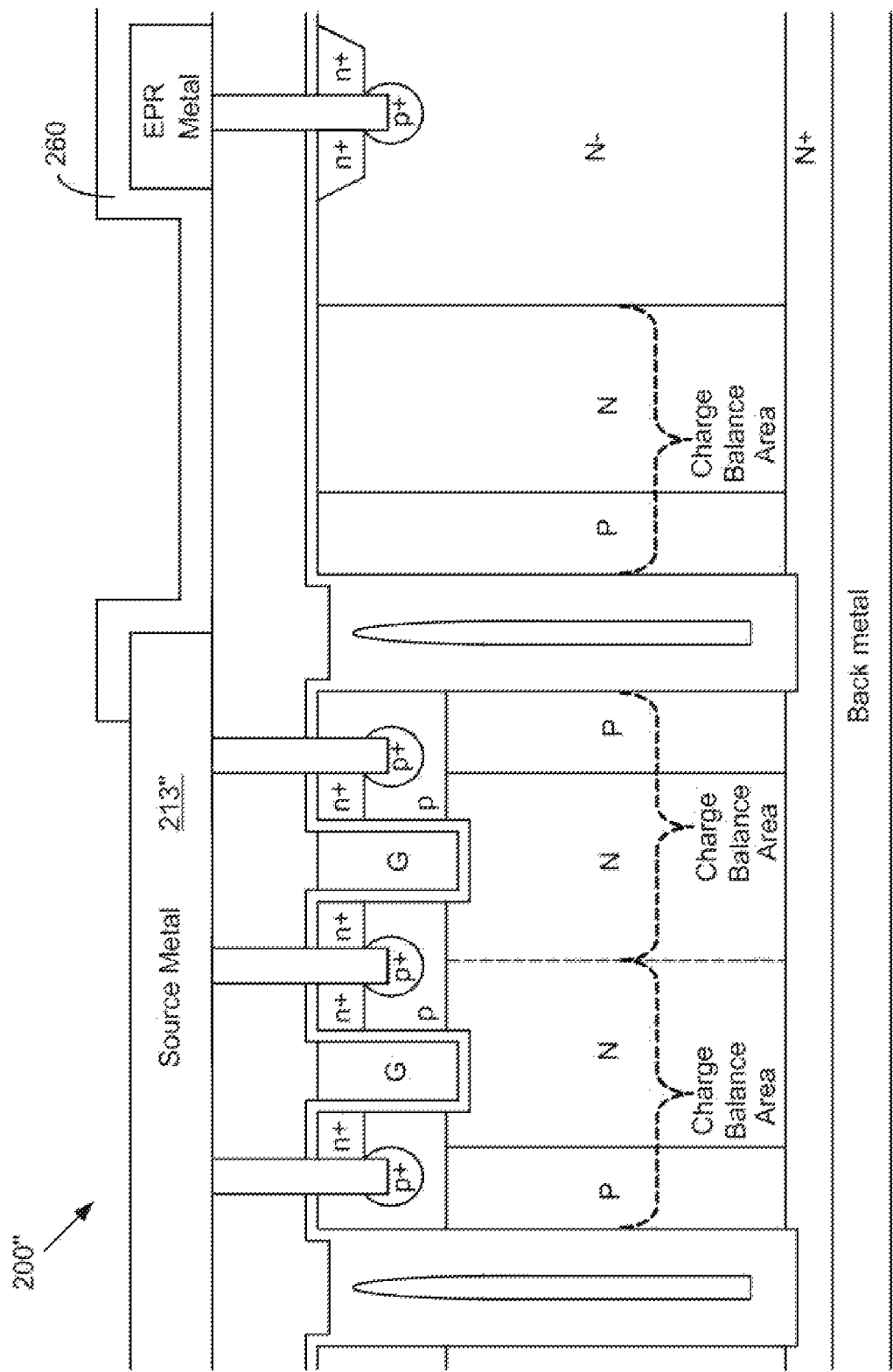


Fig.2C

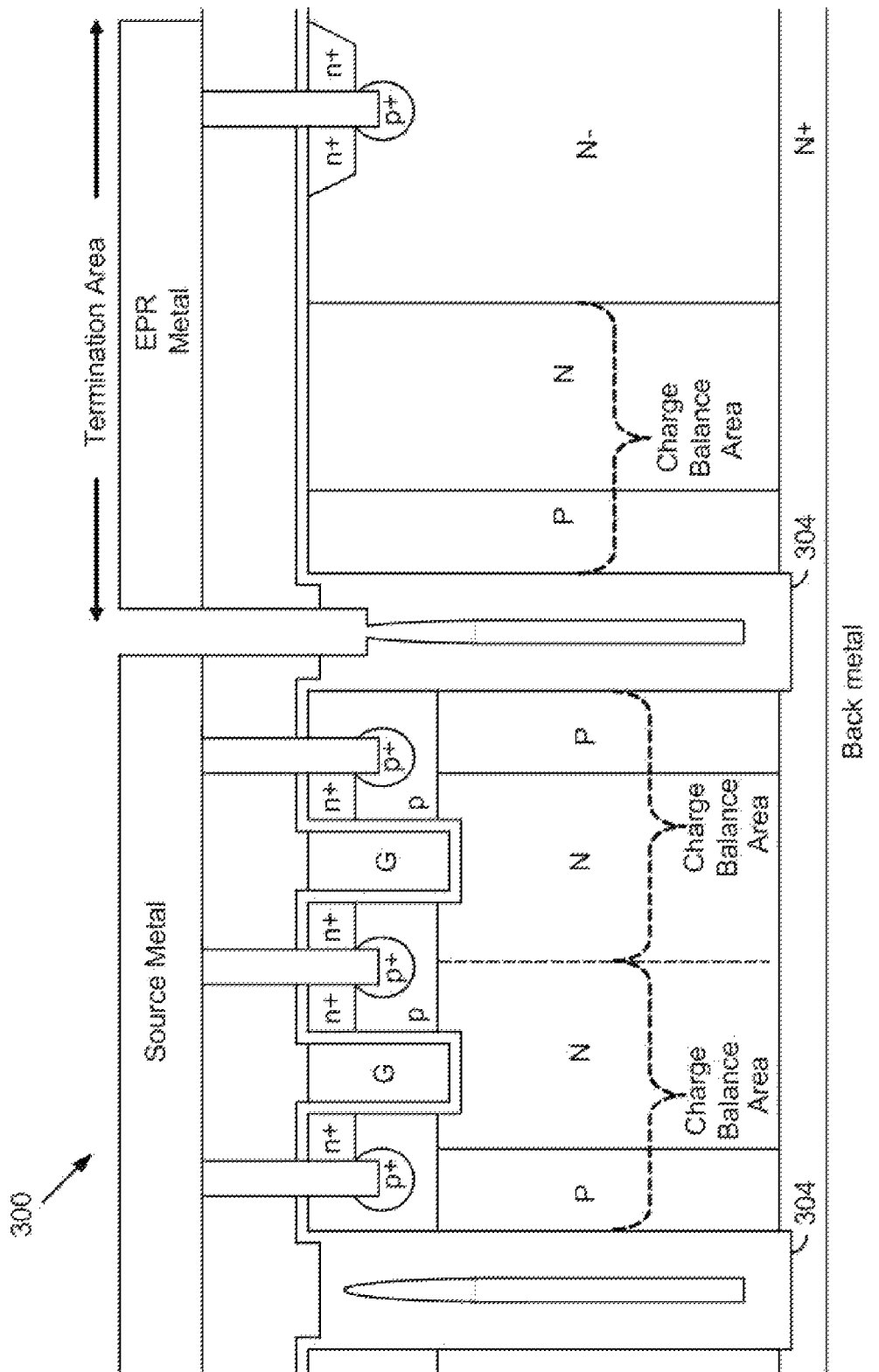


Fig.3A

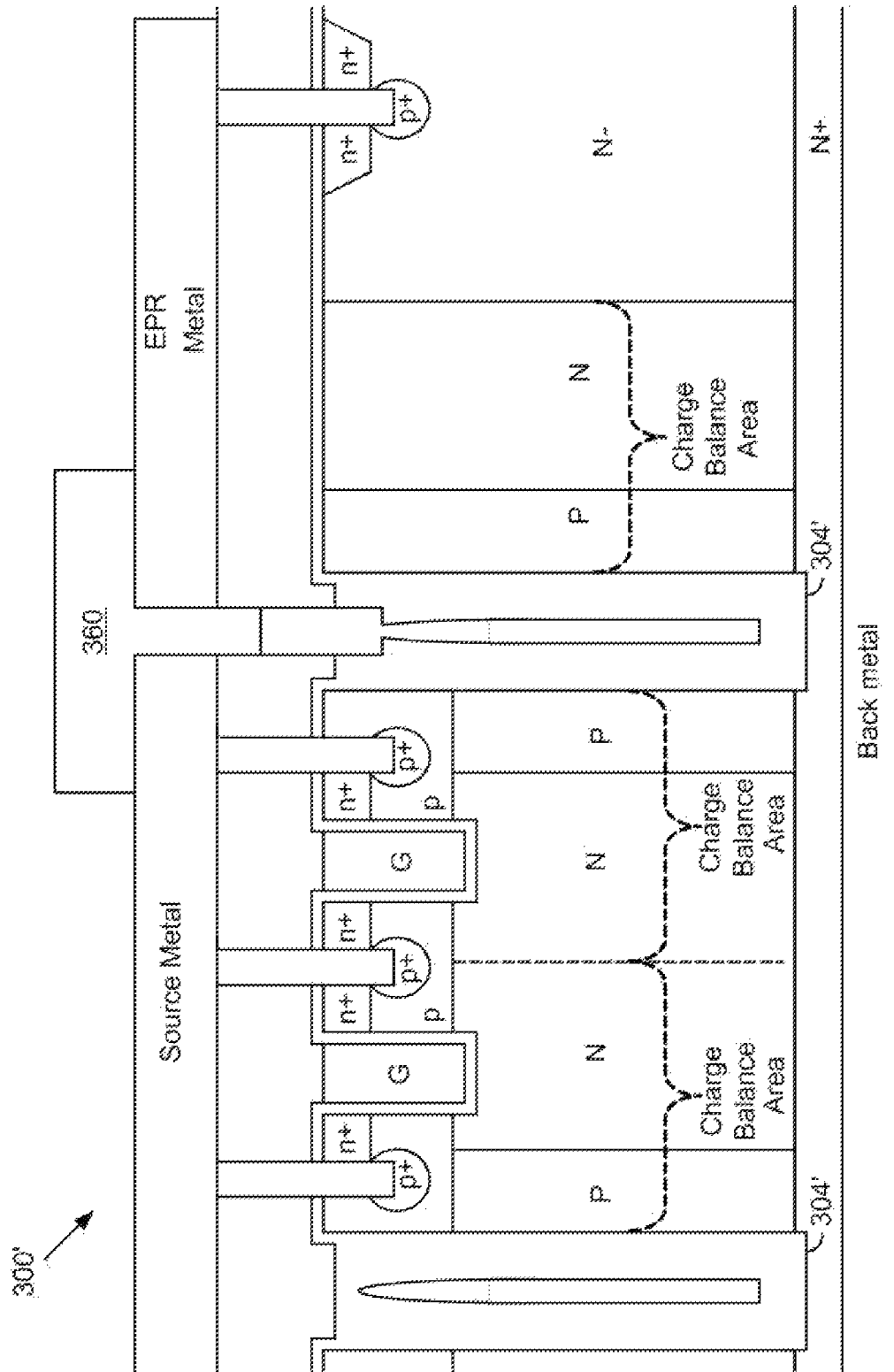


Fig.3B

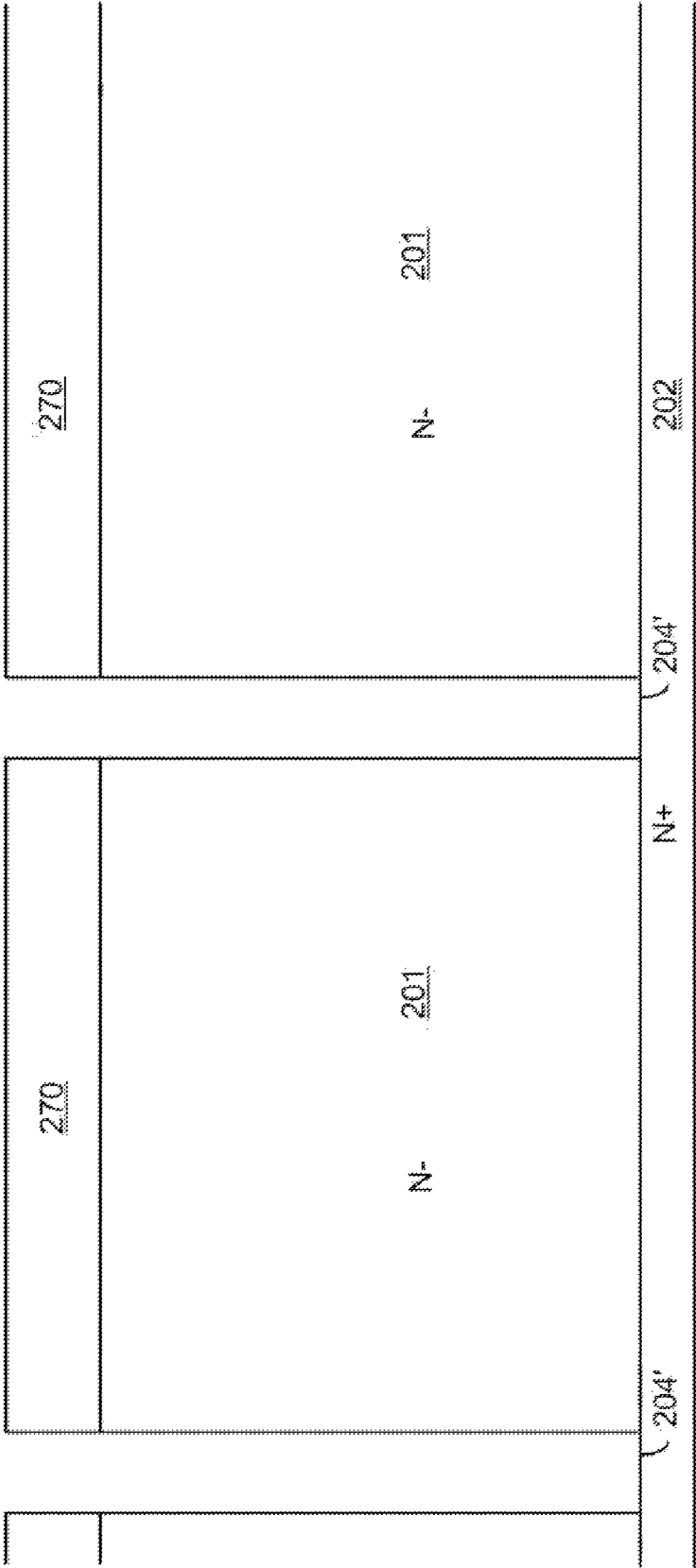
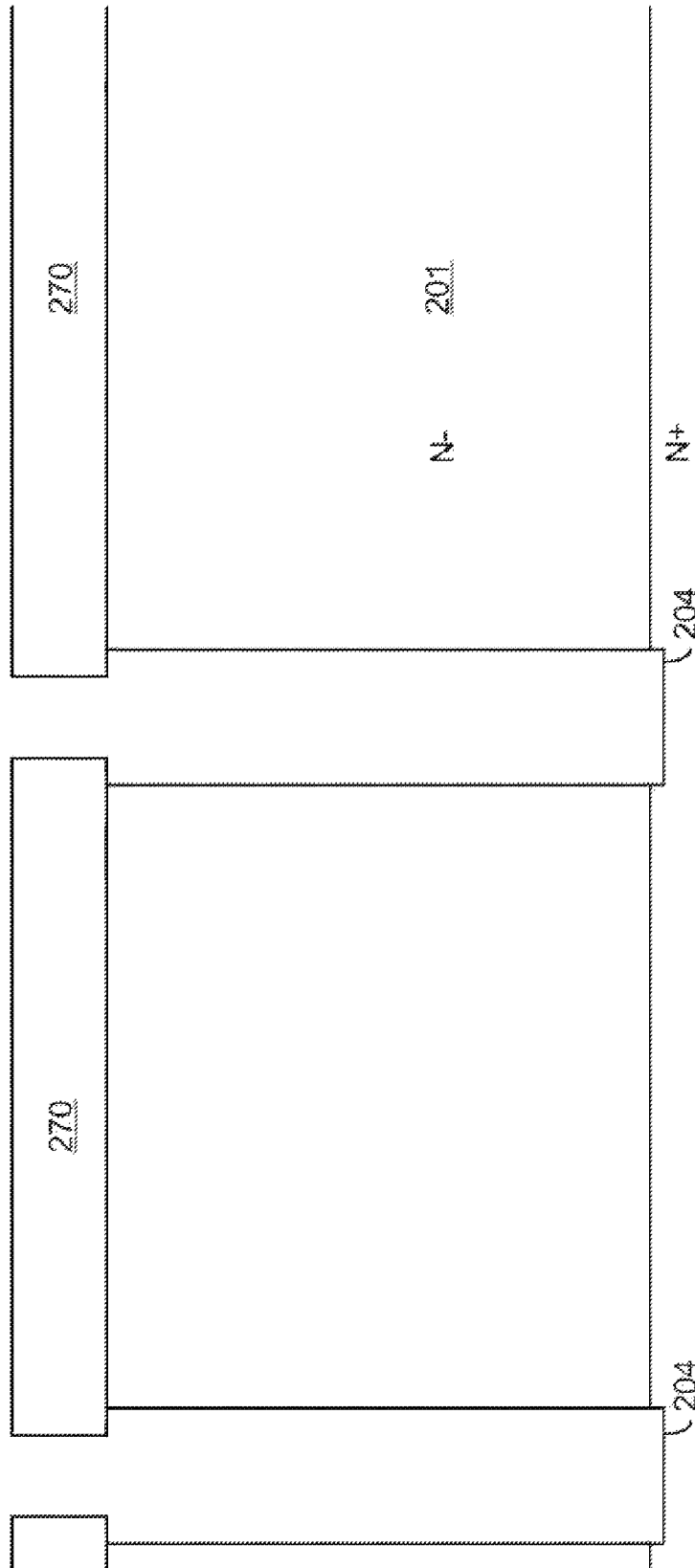


Fig. 4A



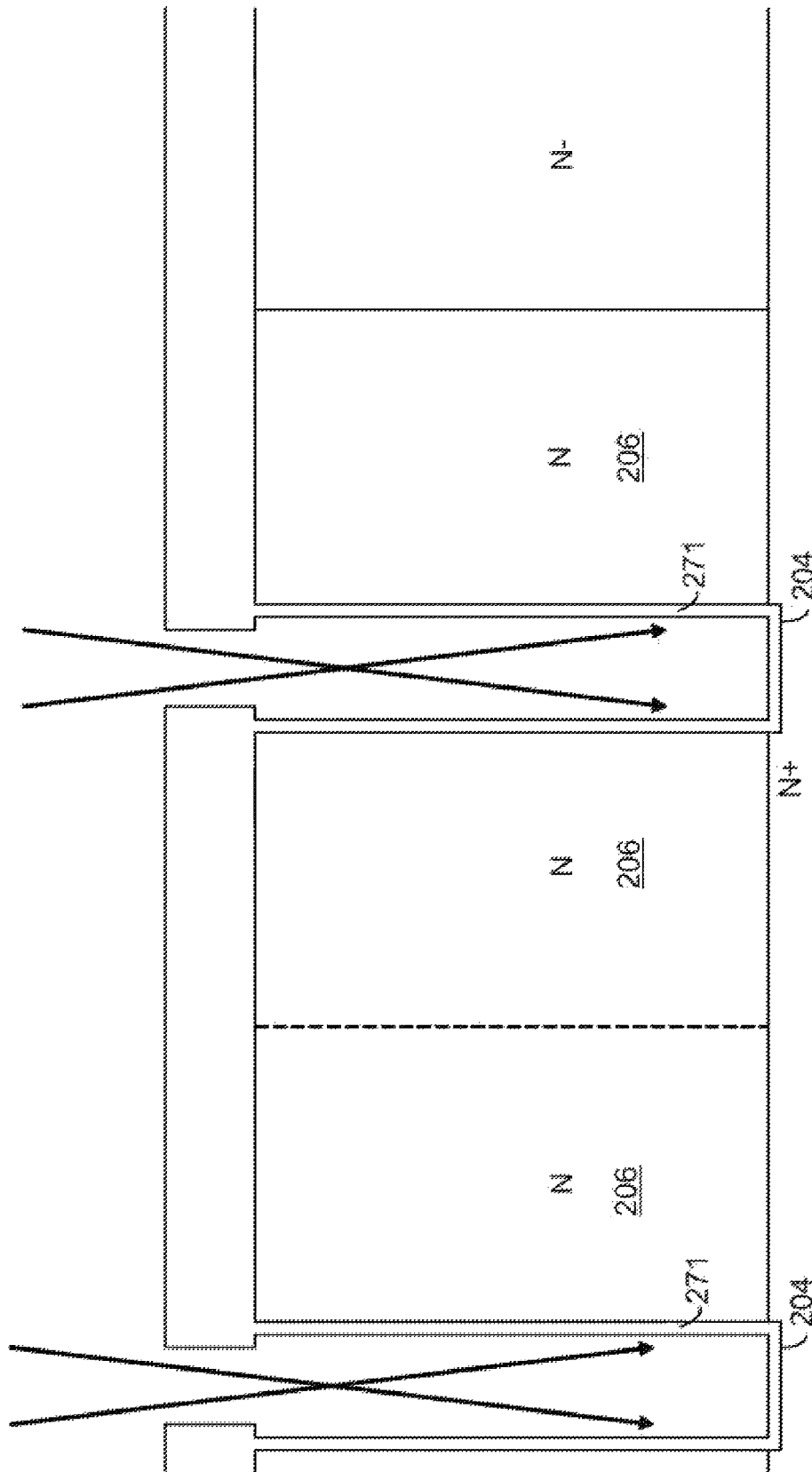
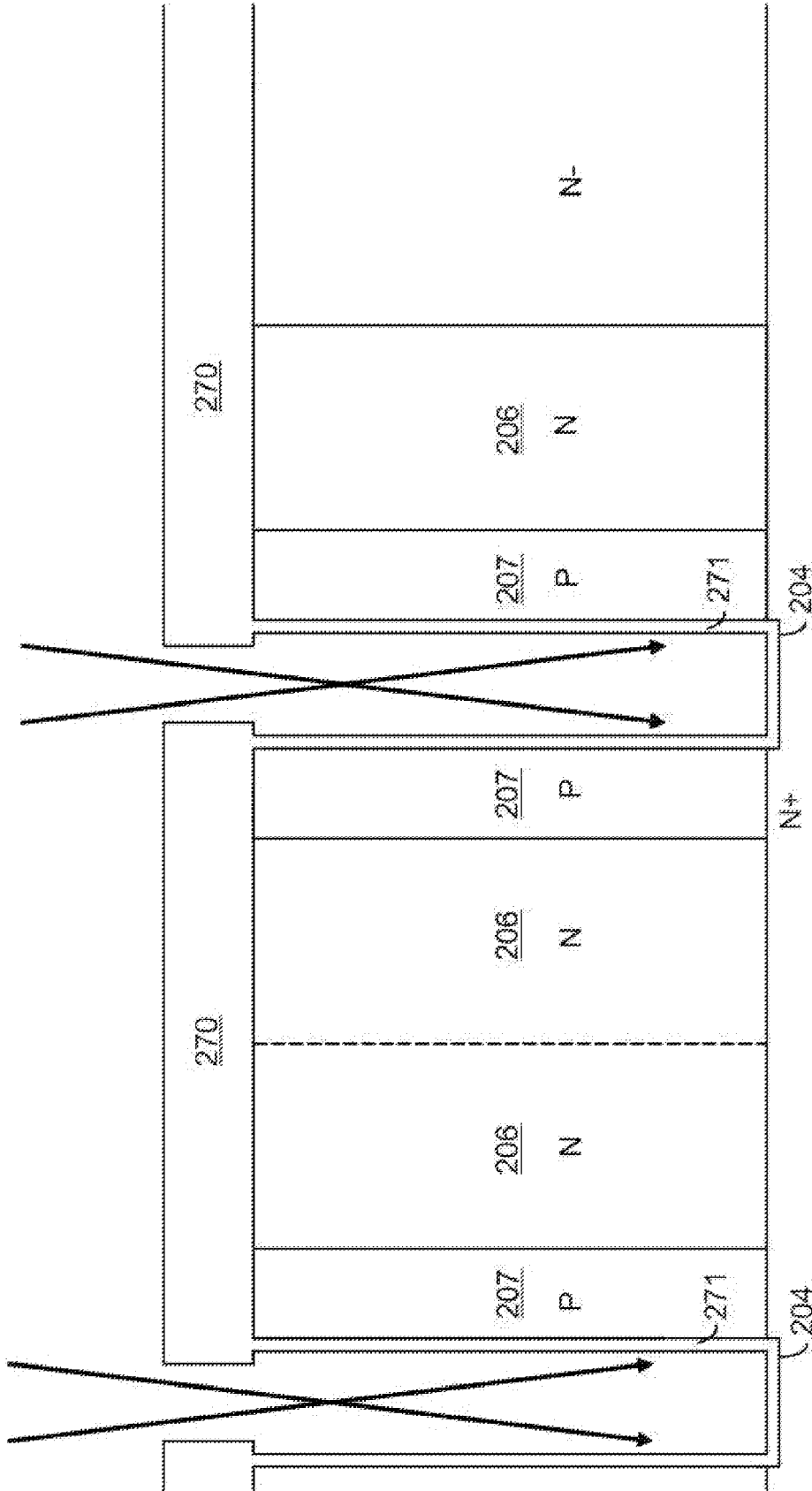


Fig. 4C



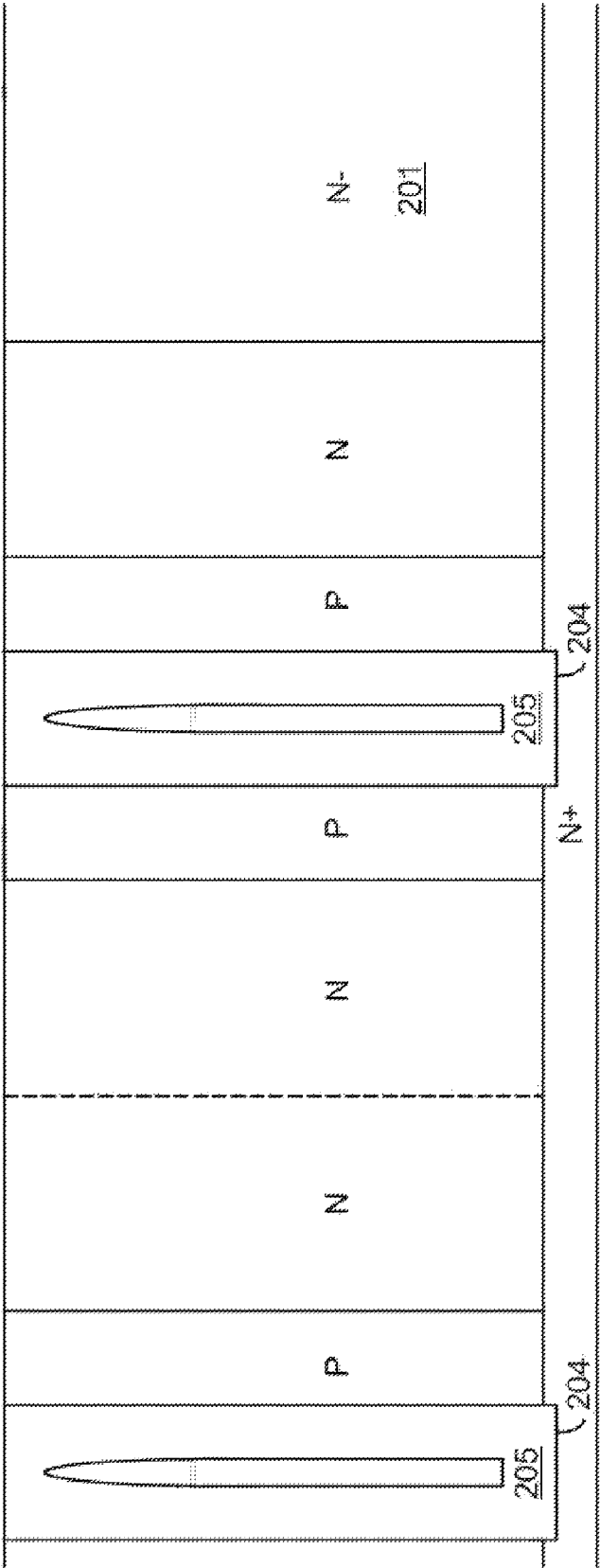


Fig.4E

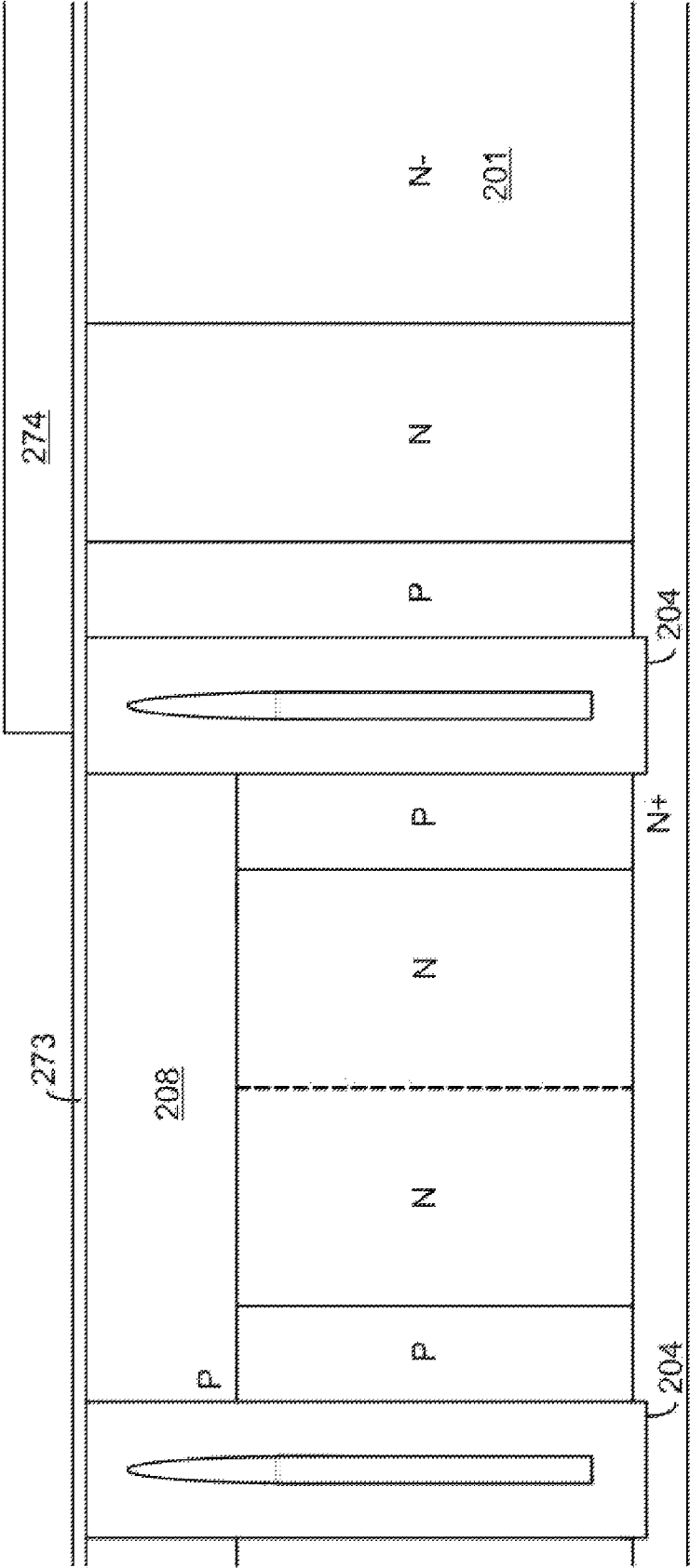


Fig.4F

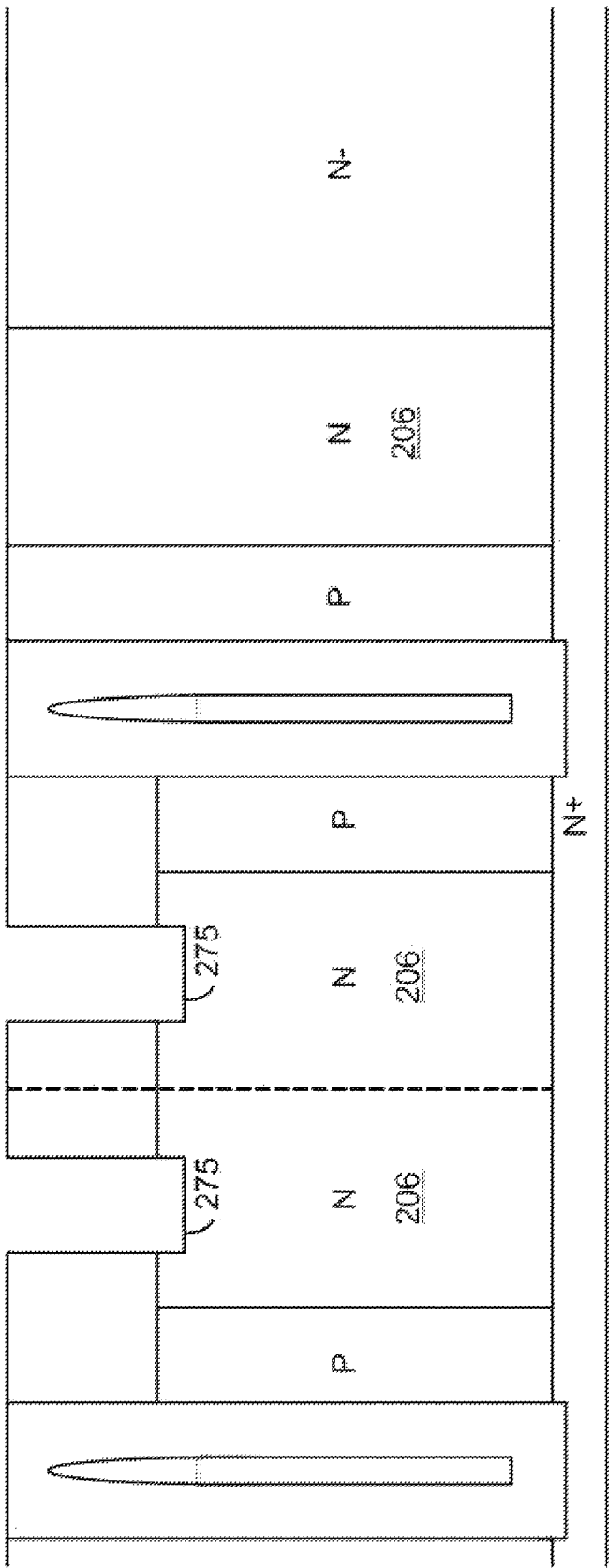


Fig. 4G

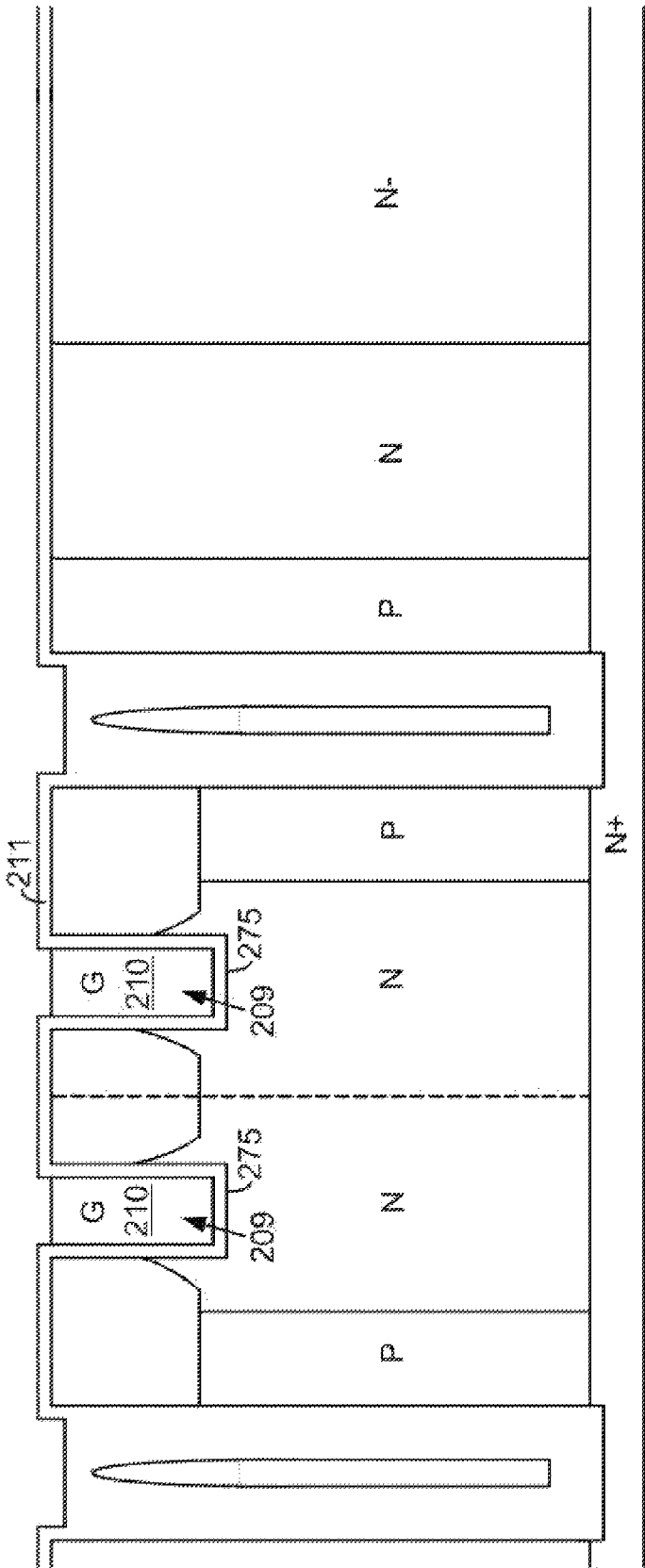


Fig. 4H

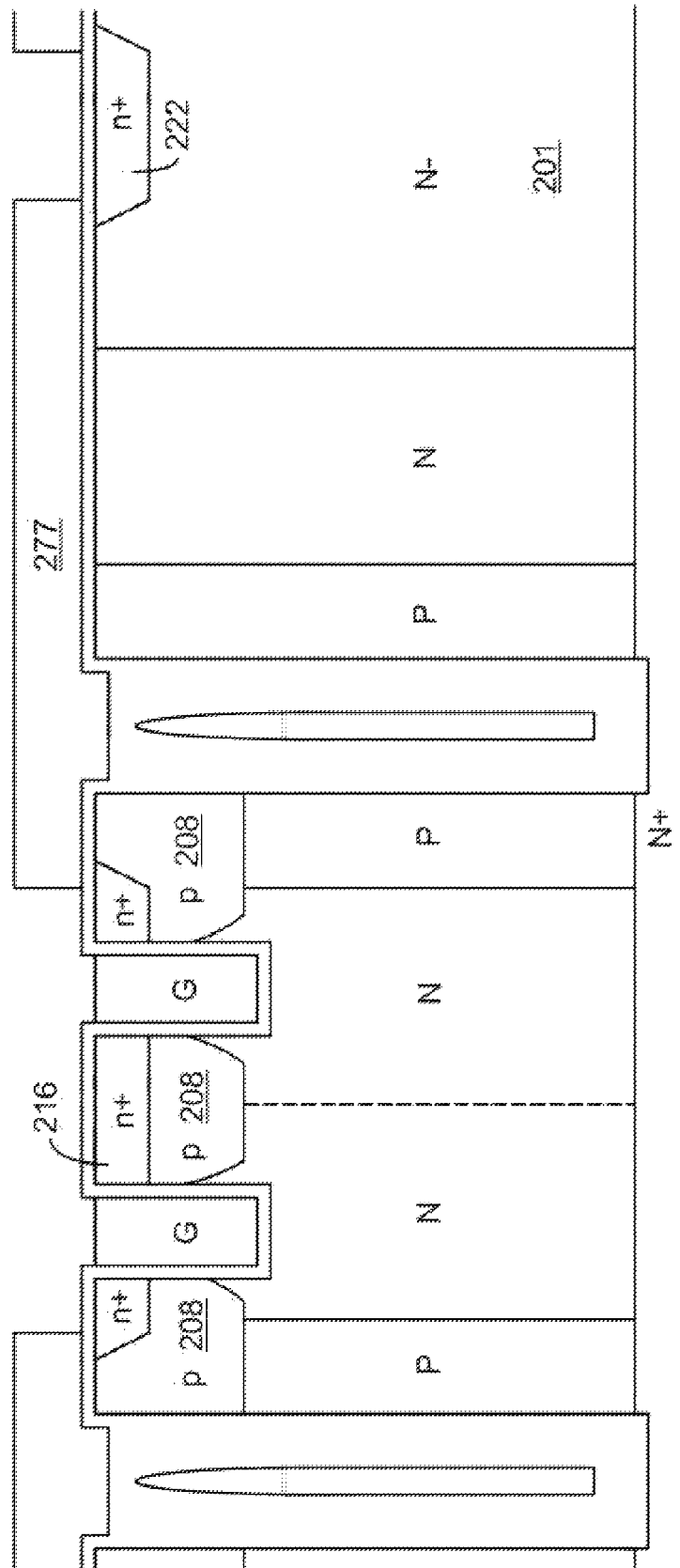


Fig. 4I

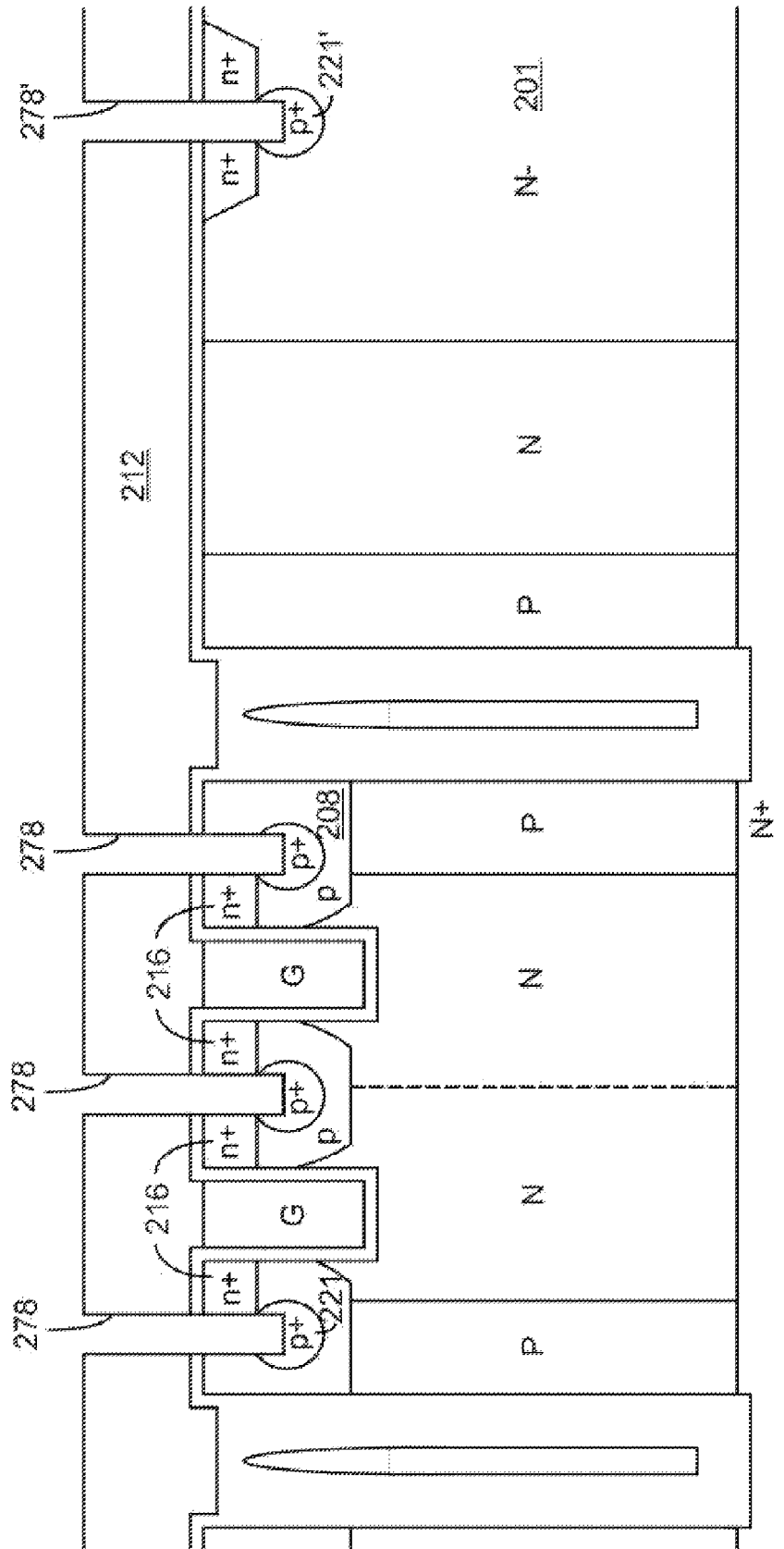


Fig. 4J

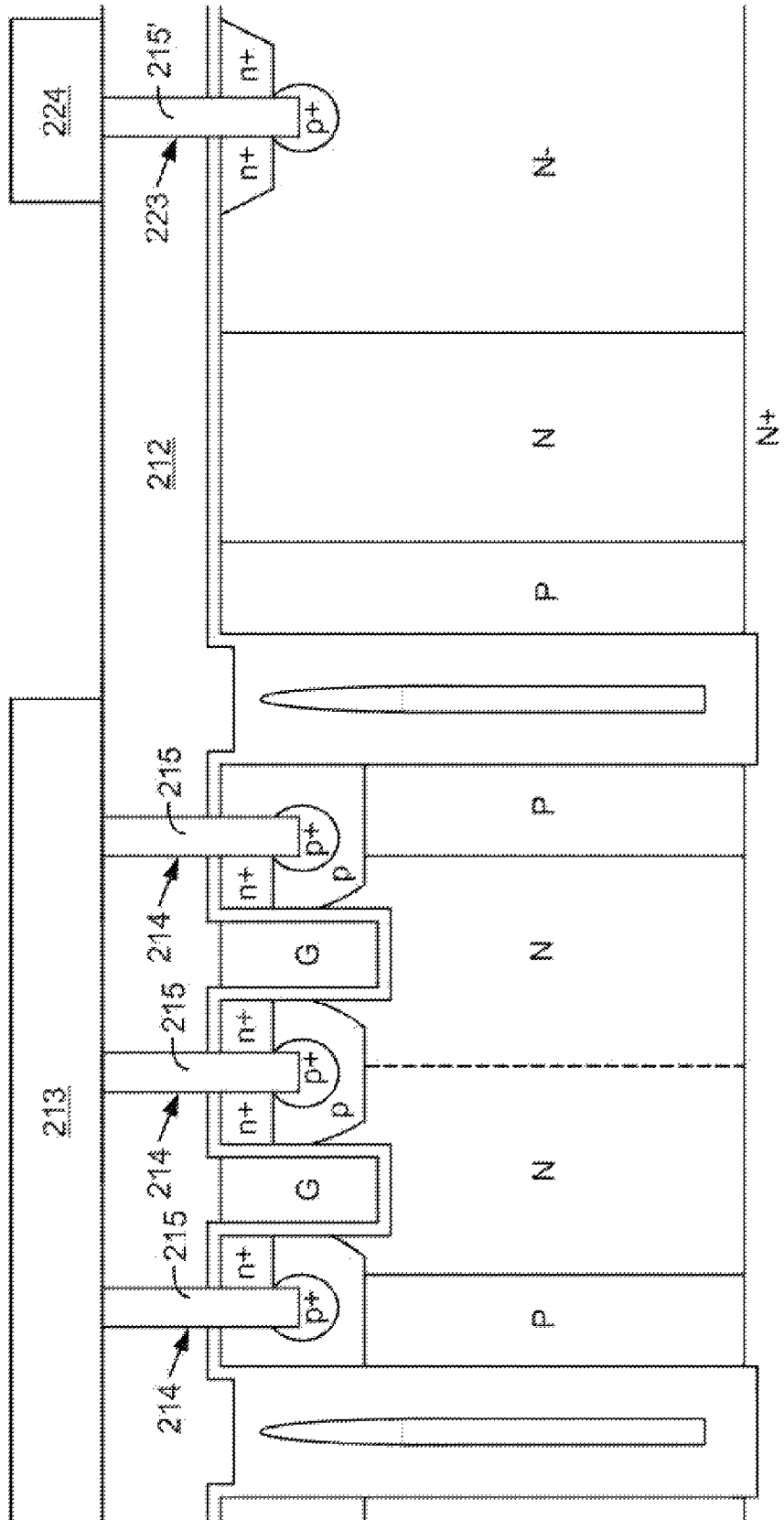


Fig. 4K

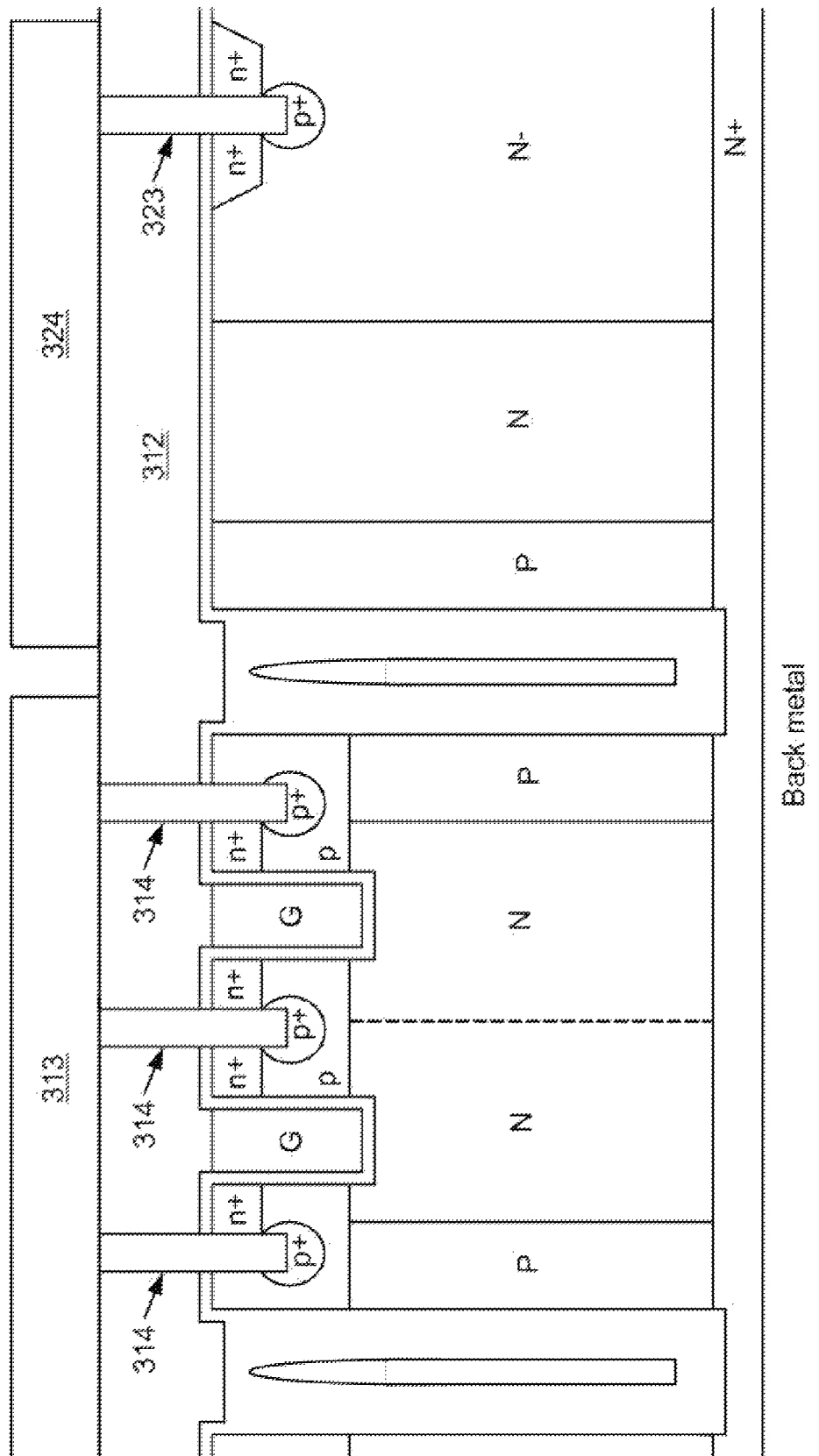


Fig. 5A

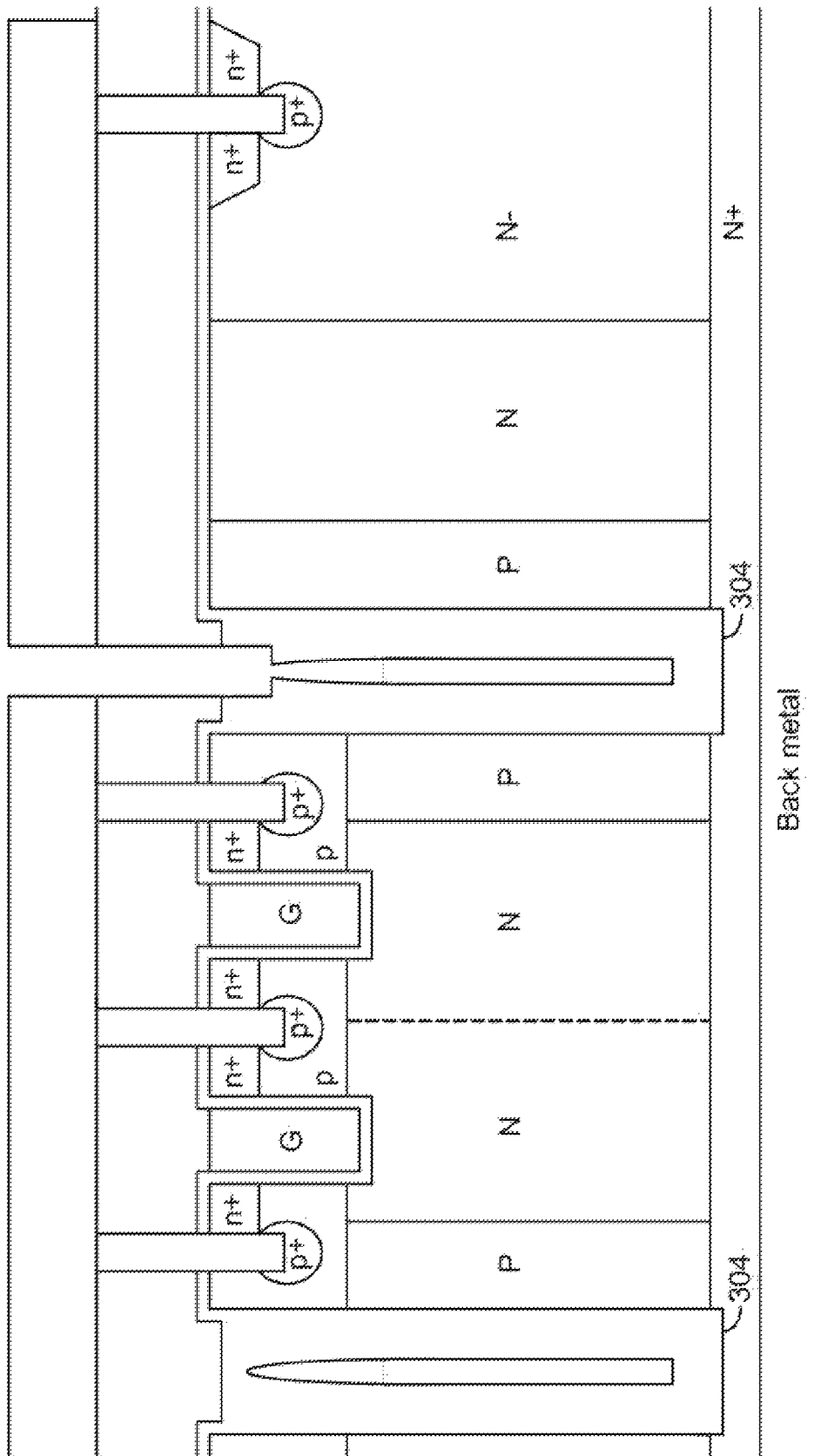


Fig. 5B

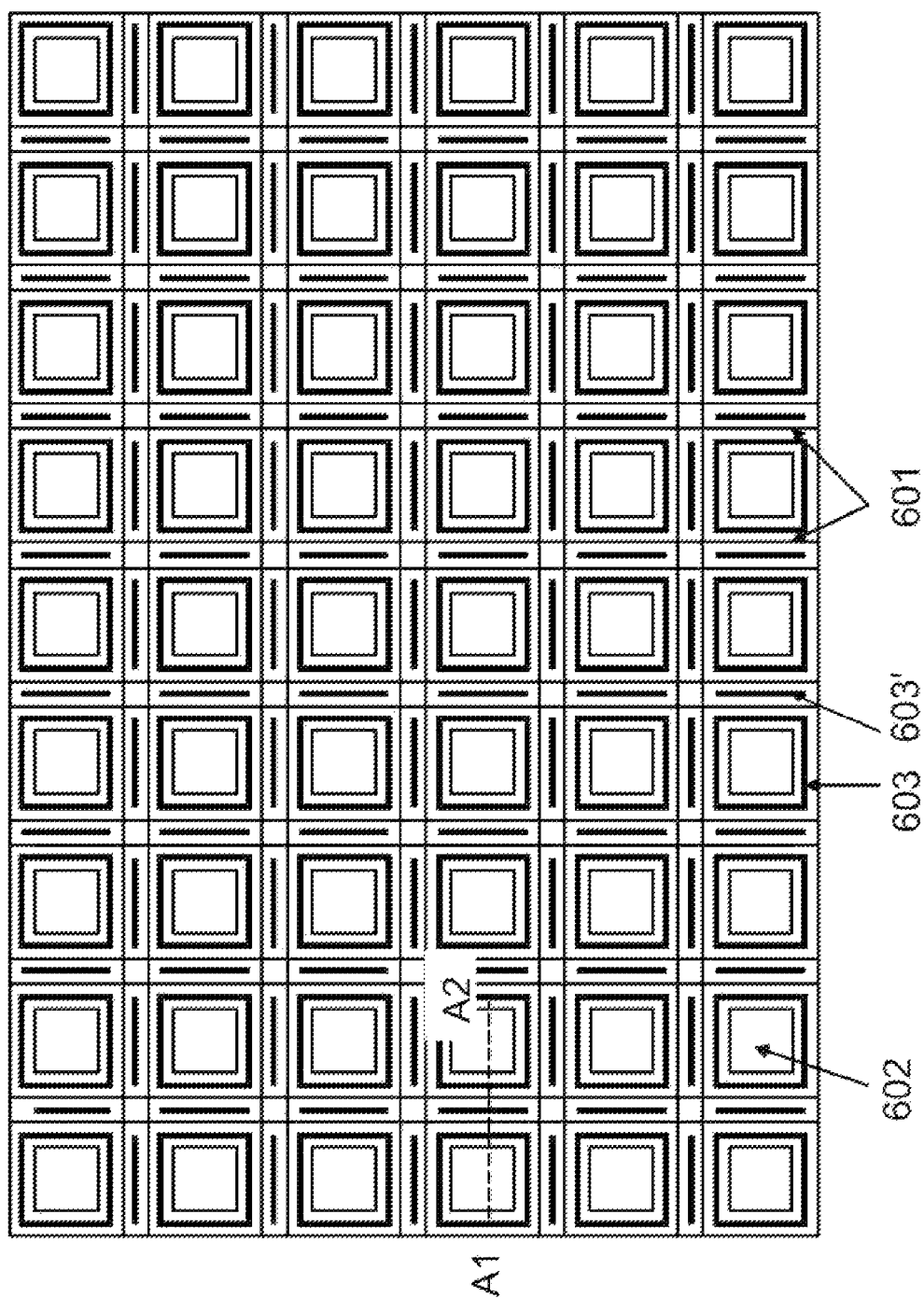


Fig. 6

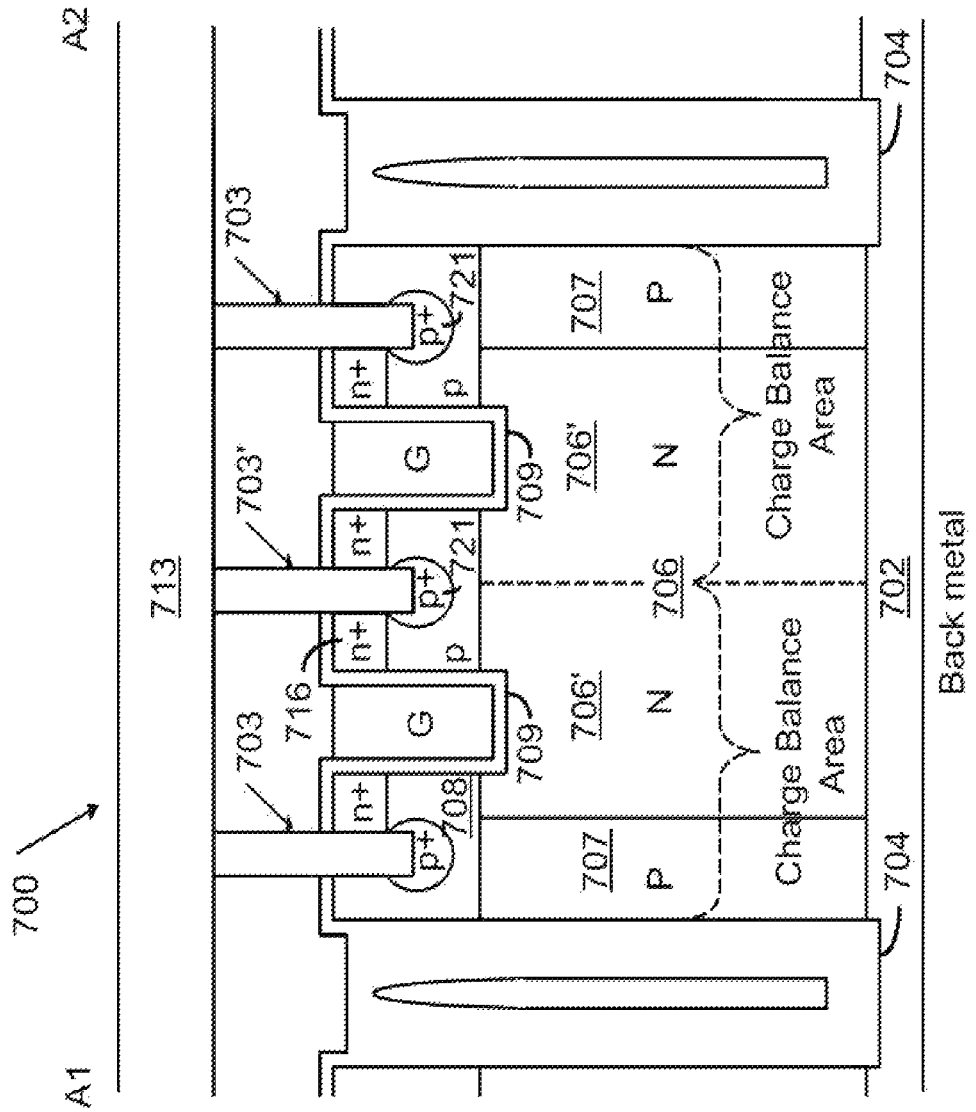


Fig. 7

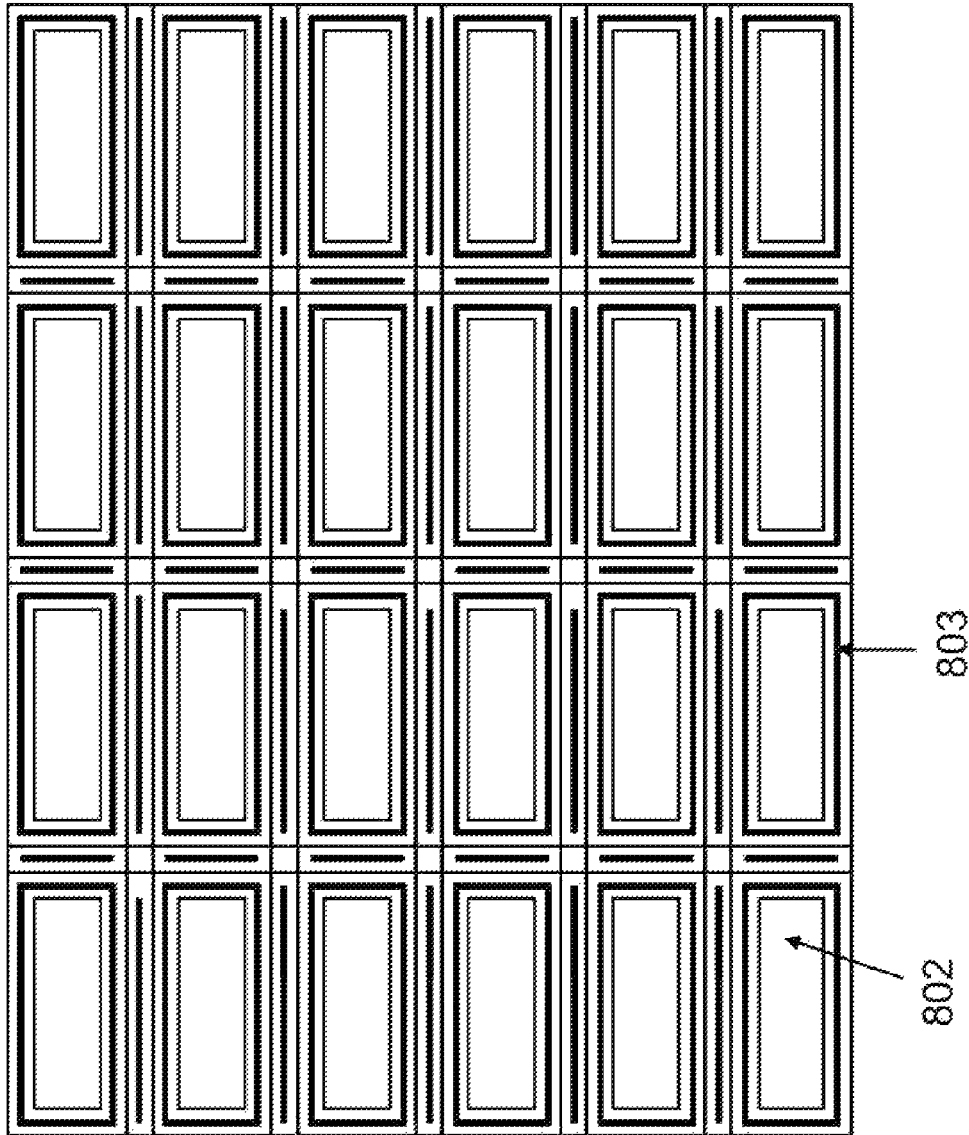


Fig. 8

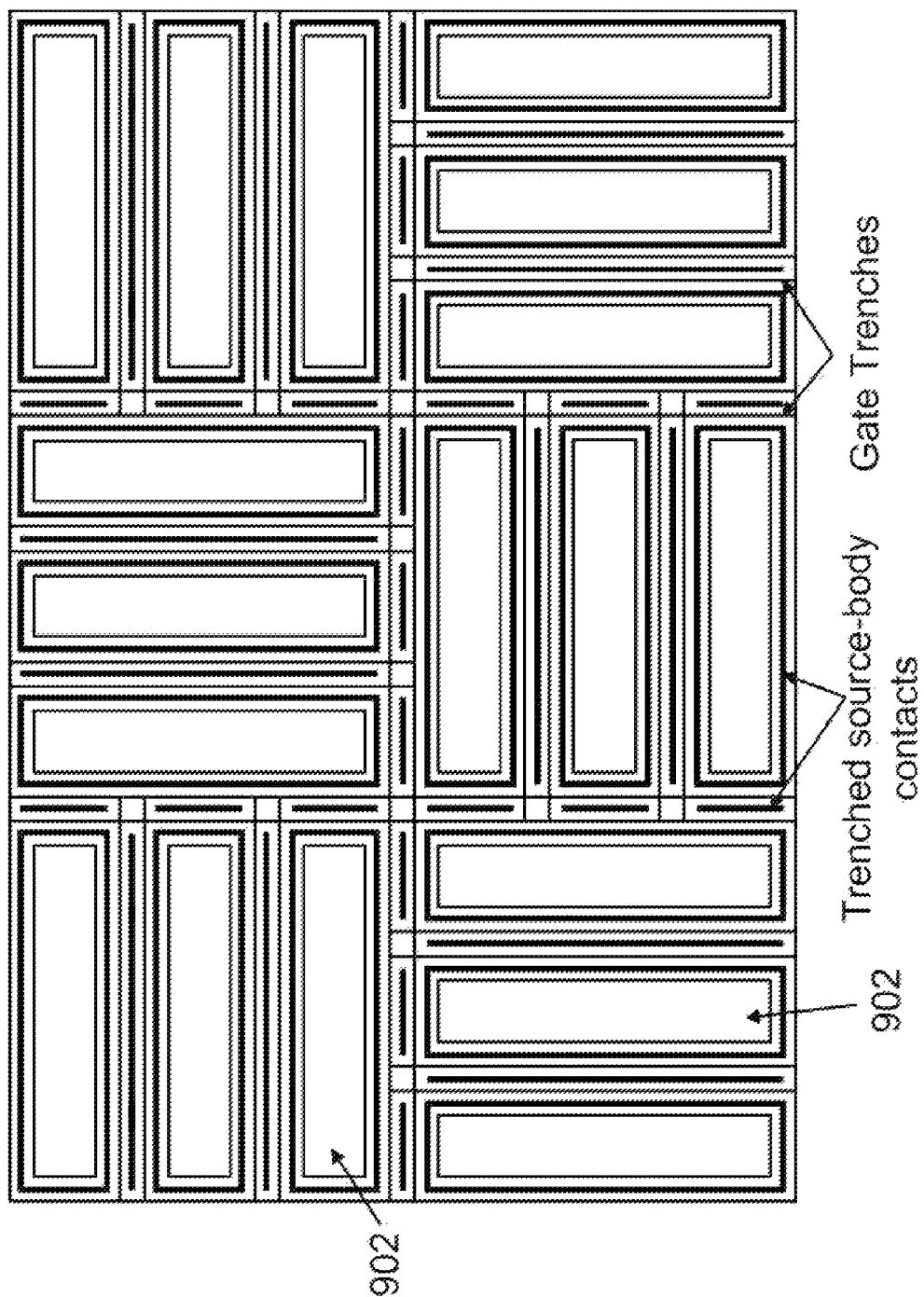


Fig.9

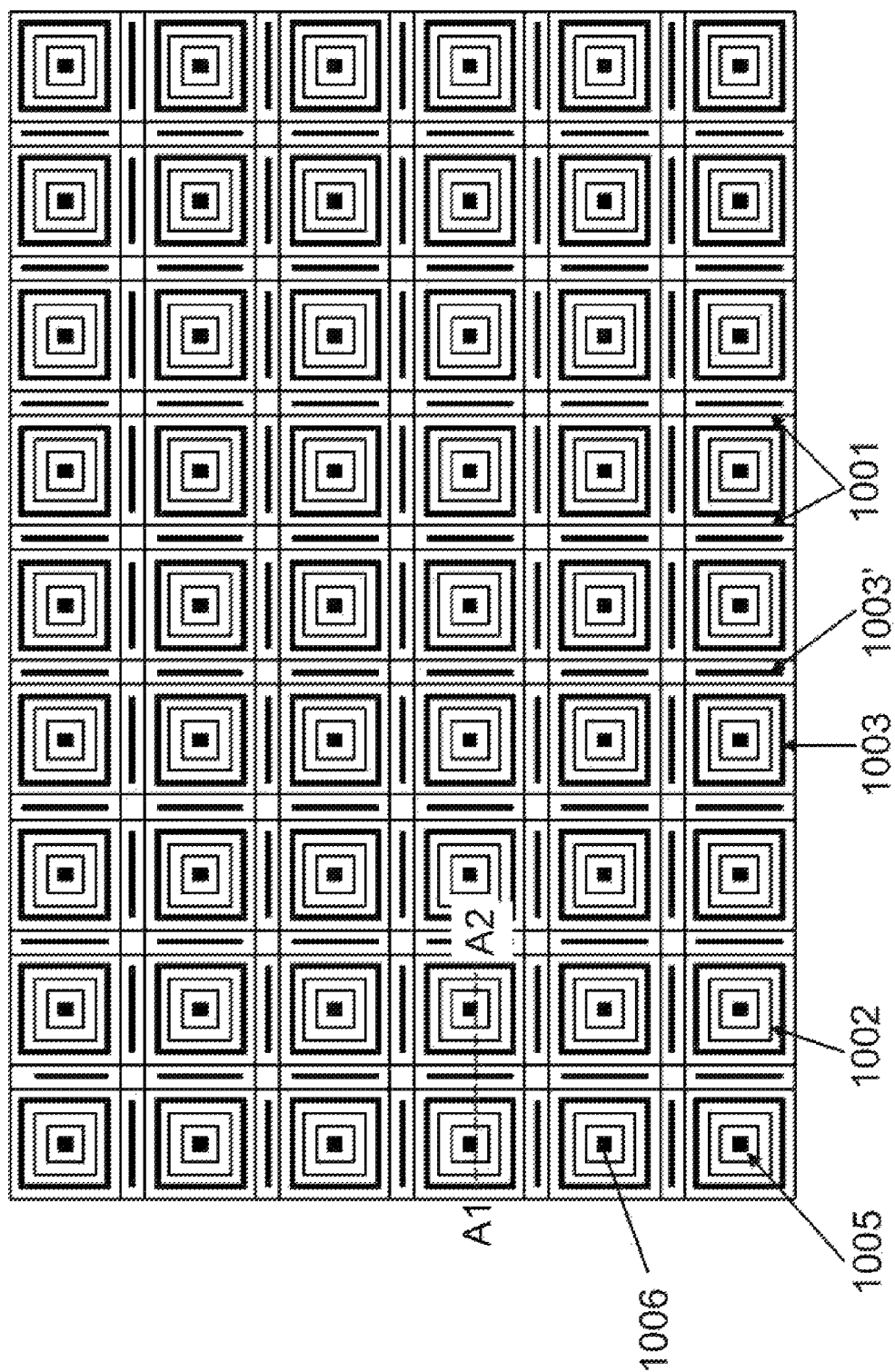


Fig. 10

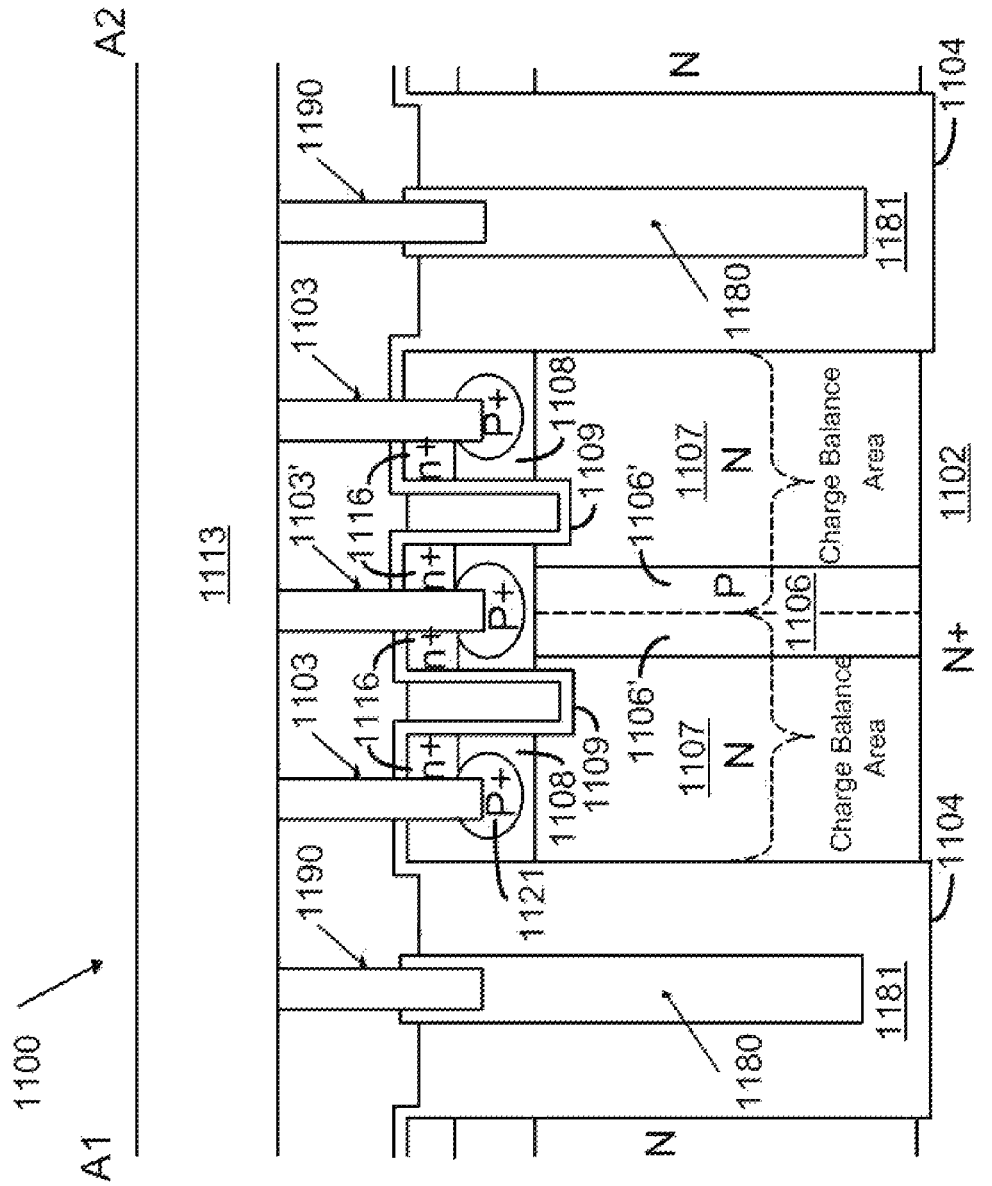


Fig.11

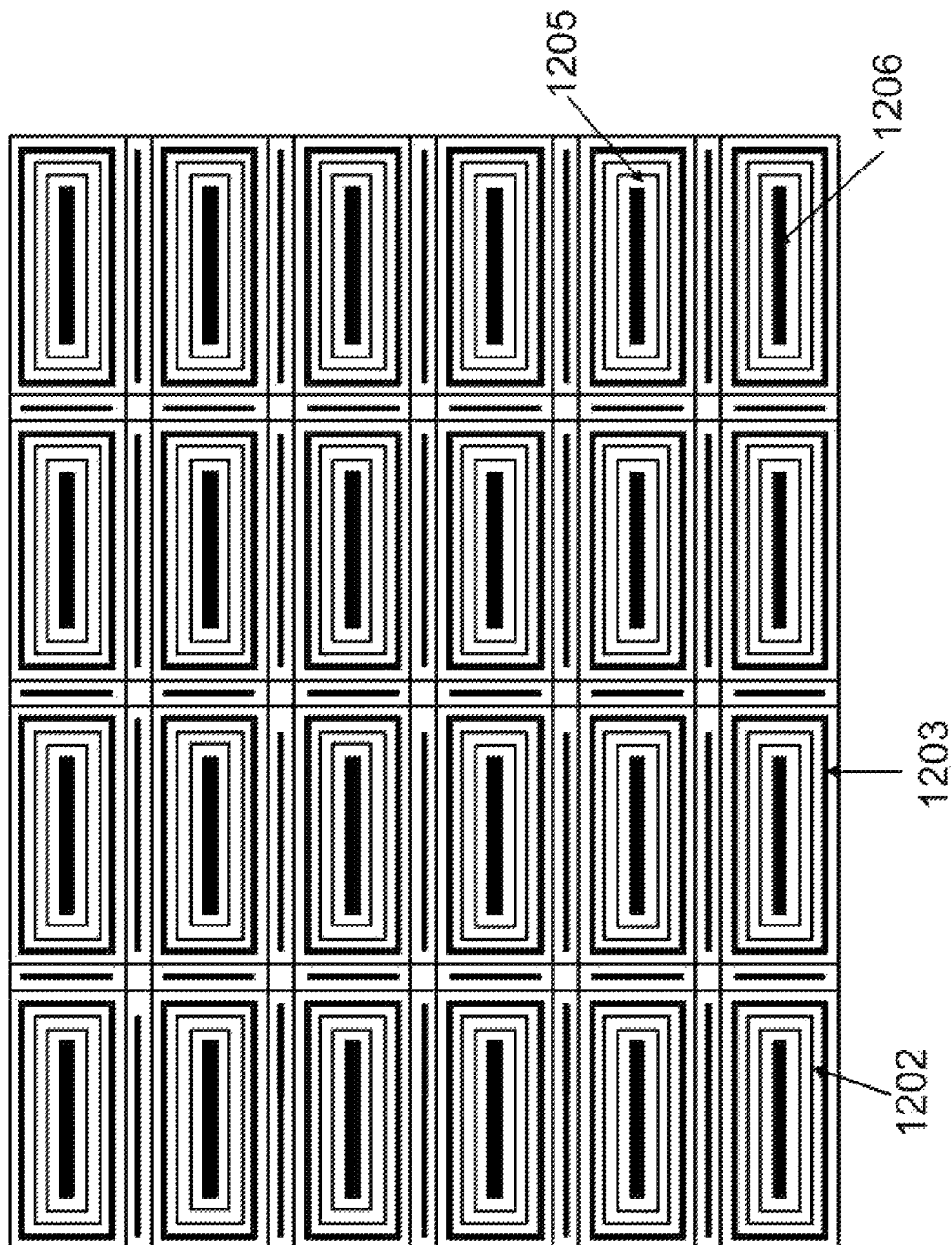


Fig. 12

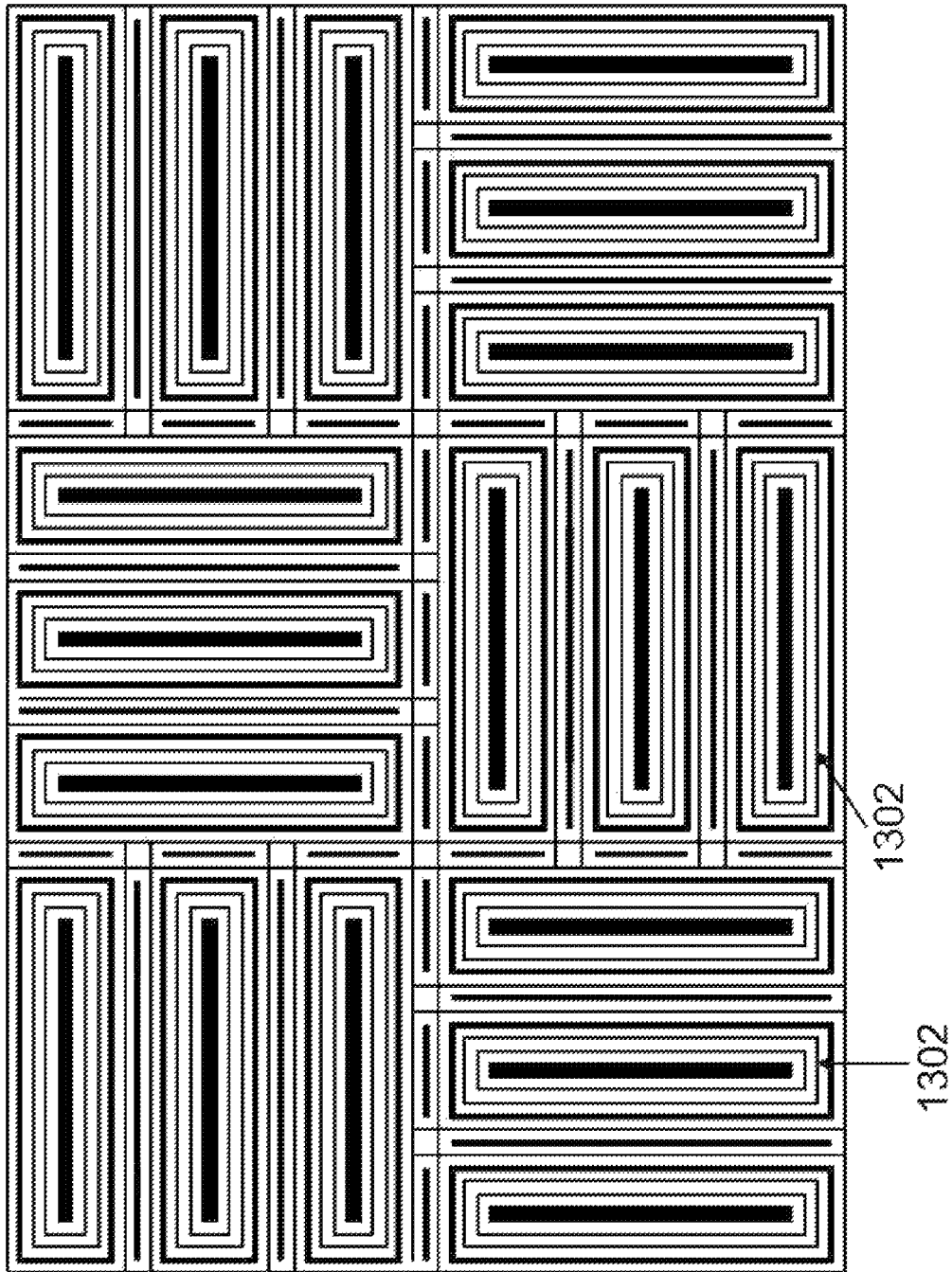


Fig. 13

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SUPER-JUNCTION TRENCH MOSFETS WITH CLOSED CELL LAYOUT HAVING SHIELDED GATE

CROSS REFERENCE TO RELATED APPLICATIONS

This application is a Continuation-In-Part (CIP) of U.S. patent application Ser. No. 14/559,061 of the same inventor, filed on Dec. 3, 2014, entitled "super-junction trench MOSFETs with closed cell layout".

FIELD OF THE INVENTION

This invention relates generally to the cell structure, device configuration and fabrication process of semiconductor power devices. More particularly, this invention relates to a novel and improved cell structure, device configuration and improved process of a super junction trench metal oxide semiconductor field effect transistor (MOSFET, the same hereinafter).

BACKGROUND OF THE INVENTION

Compared with the conventional trench MOSFETs, super-junction trench MOSFETs are more attractive due to higher breakdown voltage and lower specific R_{ds} (drain-source resistance). As shown in FIG. 1, U.S. patent application Ser. No. 13/751,458 of the same inventor as the present invention discloses a super-junction trench MOSFET 100 comprising a termination area including multiple guard rings ("GR", as illustrated in FIG. 1), wherein the termination area is about 200 μm in length due to the multiple guard rings. However, for the integration of semiconductor power devices is more and more advanced, a super-junction trench MOSFET with short termination is admired because it takes up less space and is more cost effective due to its smaller device size.

Therefore, there is still a need in the art of the semiconductor power device, particularly for super-junction trench MOSFET design and fabrication, to provide a novel cell structure, device configuration and fabrication process that would resolve these difficulties and design limitations.

SUMMARY OF THE INVENTION

The present invention provides a super-junction trench MOSFET having short termination about 20 μm in length, shortening termination length to about one tenth compared with the prior art, which is more flexible in applications and more cost effective due to its smaller device size.

According to an aspect, the present invention features a super junction trench MOSFET comprising a plurality of unit cells with each unit cell in an active area having a first type charge balance area consist of two P/N charge balance areas formed in the mesa area between adjacent deep trenches, comprising: a substrate of a first conductivity type; an epitaxial layer of the first conductivity type grown on the substrate, the epitaxial layer having a lower doping concentration than the substrate; a plurality of deep trenches filled with dielectric material, starting from a top surface of the epitaxial layer and down extending into the substrate, each comprising a void inside the dielectric material; a mesa between the pair of deep trenches; a first doped column region of the first conductivity type with column shape within each the mesa; a pair of second doped column regions of a second conductivity type with column shape adjacent to sidewalls of the pair of deep trenches within the mesa, in parallel with and surround-

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ing the first doped column region forming a first type charge balance area in conjunction with the first doped column region; a body region of the second conductivity type in the mesa, covering a top surface of the first and second doped column regions, extending between the deep trenches; at least one gate trench filled with doped poly-silicon layer padded by a gate oxide layer, starting from the top surface of the epitaxial layer and down penetrating through the body region and extending into the first doped column in the mesa; multiple 5 10 15 20 25 30 35 40 45 50 55 60 65

trenched source-body contacts with each filled with a contact metal plug extending into the body region in the mesa; a source region of the first conductivity type surrounding an upper portion of each the gate trench, extending between the upper portion of each the gate trench and sidewalls of adjacent 15 20 25 30 35 40 45 50 55 60 65

trenched source-body contacts; and a termination area comprising a second type P/N charge balance area and a channel stop region formed near the top surface of the epitaxial layer with a doping concentration higher than the epitaxial layer.

According to another aspect of the present invention, in some preferred embodiments, the third doped column region in the termination area has about half column width of the first doped column region and the fourth doped column region has about same column width as the second doped column region in the unit cells.

According to another aspect of the present invention, in some preferred embodiments, the channel stop region has a 40 45 50 55 60 65

trenched termination contact penetrating through the channel stop region.

According to another aspect of the present invention, in some preferred embodiments, the super-junction trench MOSFET further comprises a body contact region of the second conductivity type surrounding at least bottom of each of the multiple 30 35 40 45 50 55 60 65

trenched source-body contacts, wherein the body contact region has a higher doping concentration than the body region.

According to another aspect of the present invention, in some preferred embodiments, the super-junction trench MOSFET further comprises a body contact region of the second conductivity type surrounding at least bottom of the 40 45 50 55 60 65

trenched termination contact, wherein the body contact region has a higher doping concentration than the body region.

According to another aspect of the present invention, in some preferred embodiments, the contact metal plug is a tungsten plug padded by a barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN.

According to another aspect of the present invention, in some preferred embodiments, the super-junction trench MOSFET further comprises an equal potential ring metal 50 55 60 65

covering the trenched termination contact in the termination area and a passivation layer covering a top surface of the termination area.

According to another aspect of the present invention, in some preferred embodiments, the void inside the deep trench in the termination area is not opened up in air.

According to another aspect of the present invention, in some preferred embodiments, the void inside the deep trench in the termination area is opened up in air. And in some preferred embodiments, the super-junction trench MOSFET 60 65

further comprises a passivation layer covering above the void inside the deep trench in the termination area.

The present invention also features a method for manufacturing a super-junction trench MOSFET comprising the steps of: forming a plurality of deep trenches in active area inside an epitaxial layer of a first conductivity type onto a substrate of the first conductivity type; carrying out angle ion implanta-

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tions of the first conductivity type dopant and diffusion through the deep trenches to form a first doped column region of the first conductivity type with column shape within a mesa area between every two adjacent of the deep trenches; carrying out angle ion implantations of a second conductivity type dopant and diffusion through the deep trenches to form second doped column regions of the second conductivity type with column shape adjacent to sidewalls of the deep trenches, in parallel with and surrounding the first doped column region; forming a third doped column of the first conductivity type and a fourth doped column of the second conductivity type through a deep trench in termination area simultaneously with the first doped column and the second doped column within the mesa, respectively; depositing a dielectric material with voids in the deep trenches; removing the dielectric material from top surface of the epitaxial layer; forming a pad oxide layer prior to forming body regions; and forming a channel stop region near the top surface of the epitaxial layer in the termination area and source regions in the active area at same step by carrying out source ion implantation; depositing a contact interlayer on the top surface of the epitaxial layer; forming a trenched termination contact penetrating through the channel stop region into the epitaxial layer in the termination area and multiple trenched source-body contacts in the active area by doing successively dry oxide etch and dry silicon etch; and depositing a tungsten layer and then etching back to form contact metal plugs respectively filled in the trenched termination contacts and the multiple trenched source-body contacts.

According to another aspect of the present invention, a super-junction trench MOSFET with closed cell layout is disclosed, wherein closed gate trenches surrounding a deep trench in each unit cell. Trenched source-body contacts are disposed between the closed gate trenches and the deep trench. In some preferred embodiments, the deep trench has square, rectangular, circle or hexagon shape. In some preferred embodiments, the trenched source-body contacts have square, rectangular, circle or hexagon shape. In some preferred embodiments, trenched source-body contacts are also disposed between the adjacent closed gate trenches.

According to another aspect of the present invention, a super-junction trench MOSFET with closed cell layout having shielded gate is disclosed, wherein closed gate trenches surrounding a deep trench in each unit cell and the shielded gate disposed in the deep trench. Trenched source-body contacts are disposed between the closed gate trenches and the deep trench. In some preferred embodiments, the deep trench has square, rectangular, circle or hexagon shape. In some preferred embodiments, the trenched source-body contacts have square, rectangular, circle or hexagon shape. In some preferred embodiments, trenched source-body contacts are also disposed between the adjacent closed gate trenches.

According to another aspect of the present invention, a super-junction trench MOSFET with closed cell layout having shielded gate further comprises a substrate of a first conductivity type; an epitaxial layer of the first conductivity type grown on the substrate, the epitaxial layer having a lower doping concentration than the substrate; the deep trench having deeper trench depth than the gate trench; the shielded gate formed within the deep trench and surrounding with a dielectric material; a mesa between a pair of adjacent the deep trench; a first doped column region of a second conductivity type with column shape within each the mesa; a pair of second doped column regions of the first conductivity type with column shape adjacent to sidewalls of the pair of deep trenches within the mesa, in parallel with and surrounding the first doped column region forming a first type charge balance

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area in conjunction with the first doped column region; a body region of the second conductivity type in the mesa, covering a top surface of the first and second doped column regions, extending between the deep trenches; the gate trench filled with doped poly-silicon layer padded by a gate oxide layer having thickness thinner than the dielectric material filled into the deep trench, starting from the top surface of the epitaxial layer and down penetrating through the body region and extending into the second doped column in the mesa; the trenched source-body contacts with each filled with a contact metal plug extending into the body region in the mesa; a source region of the first conductivity type surrounding an upper portion of each the gate trench, extending between the upper portion of each the gate trench and sidewalls of adjacent trenched source-body contacts; and a source metal connected with the shielded gate and the source region.

According to another aspect of the present invention, in some preferred embodiments, the super-junction trench MOSFET further comprises a body contact region of the second conductivity type surrounding at least bottom of each of the trenched source-body contacts, wherein the body contact region has a higher doping concentration than the body region.

According to another aspect of the present invention, in some preferred embodiments, wherein the contact metal plug is a tungsten plug padded by a barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN.

These and other objects and advantages of the present invention will no doubt become obvious to those of ordinary skill in the art after having read the following detailed description of the preferred embodiment, which is illustrated in the various drawing figures.

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention can be more fully understood by reading the following detailed description of the preferred embodiments, with reference made to the accompanying drawings, wherein:

FIG. 1 is a cross-sectional view of a super junction trench MOSFET of U.S. patent application Ser. No. 13/751,458 of the same inventor.

FIG. 2A is a cross-sectional view of a preferred embodiment according to the present invention.

FIG. 2B is a cross-sectional view of another preferred embodiment according to the present invention.

FIG. 2C is a cross-sectional view of another preferred embodiment according to the present invention.

FIG. 3A is a cross-sectional view of another preferred embodiment according to the present invention.

FIG. 3B is a cross-sectional view of another preferred embodiment according to the present invention.

FIGS. 4A-4K are a serial of cross-sectional views for showing the processing steps for fabricating the super-junction trench MOSFET according to the present invention.

FIGS. 5A and 5B are cross-sectional views for showing the processing steps for forming the opened up void of another super-junction trench MOSFET according to the present invention.

FIG. 6 is a top view of super-junction trench MOSFETs with square closed cell layout.

FIG. 7 is a cross-sectional view of A1-A2 in FIG. 6.

FIG. 8 is a top view of super junction trench MOSFETs with rectangular closed cells in single orientation layout.

FIG. 9 is a top view of super junction trench MOSFETs with rectangular closed cells in multiple orientations layout.

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FIG. 10 is a top view of super-junction trench MOSFETs with square closed cell layout having shielded gate.

FIG. 11 is a cross-sectional view of A1-A2 in FIG. 10.

FIG. 12 is a top view of super-junction trench MOSFETs with rectangular closed cells having shielded gate in single orientation layout.

FIG. 13 is a top view of super-junction trench MOSFETs with rectangular closed cells having shielded gate in multiple orientations layout.

DETAILED DESCRIPTION OF THE EMBODIMENTS

In the following Detailed Description, reference is made to the accompanying drawings, which forms a part thereof, and in which is shown by way of illustration specific embodiments in which the invention may be practiced. In this regard, directional terminology, such as “top”, “bottom”, “front”, “back”, etc., is used with reference to the orientation of the Figure(s) being described. Because components of embodiments can be positioned in a number of different orientations, the directional terminology is used for purpose of illustration and is in no way limiting. It is to be understood that other embodiments may be utilized and structural or logical changes may be made without departing from the scope of the present invention. The following detailed description, therefore, is not to be taken in a limiting sense, and the scope of the present invention is defined by the appended claims. It is to be understood that the features of the various exemplary embodiments described herein may be combined with each other, unless specifically noted otherwise.

Please refer to FIG. 2A for a preferred embodiment of this invention wherein an N-channel super-junction trench MOSFET 200 is formed in an N- epitaxial layer 201 supported onto an N+ substrate 202 which coated with a back metal 203 of Ti/Ni/Ag on its rear side as drain metal. The N-channel super junction trench MOSFET 200 comprises a plurality of unit cells with each comprising a plurality of deep trenches 204 formed starting from a top surface of the N- epitaxial layer 201 and vertically down extending into the N+ substrate 202. Inside each of the deep trenches 204, a thick dielectric layer 205 with a buried void is formed therein. A mesa is therefore formed between every two adjacent of the deep trenches 204 in each unit cell wherein an N first doped column region 206 consist of two N sub-doped column regions 206' each having half column width of the N first doped column region 206 is formed. Adjacent to sidewalls of the deep trenches 204, a pair of P second doped column regions 207 is formed in the mesa and in parallel surrounding with the N first doped column region 206. A first type charge balance area comprising two P/N charge balance areas is formed in the mesa area between the adjacent deep trenches. The N first doped column region 206 and the P second doped column regions 207 all have column bottoms above trench bottoms of the deep trenches 204. Onto a top surface of the N first doped column region 206 and the P second doped column regions 207, a p body region 208 is formed between in the mesa extending between every two adjacent of the deep trenches 204. A pair of gate trenches 209 are penetrating through the p body region 208 further extending into the N first doped column region 206 in each unit cell, wherein the pair of gate trenches 209 each comprises a gate electrode 210 padded by a gate oxide layer 211. In some preferred embodiments, there is only one gate trench penetrating through the p body region further extending into the N first doped column region in each unit cell as an alternative. Onto a top surface of the gate electrodes 210, the contact interlayer 212 is formed to isolate

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the gate electrodes 210 from the source metal 213. In each the mesa, multiple trenched source-body contacts 214 with each filled with a tungsten plug 215 are formed penetrating through the contact interlayer 212 and extending into the p body region 208 in each unit cell, and an n+ source regions 216 is formed surrounding an upper portion of the gate trenches 209, extending between the upper portion of the gate trenches 209 and sidewalls of adjacent trenched source-body contacts 214. Therefore, the p body region 208 and the n+ source region 216 are connected to the source metal 213 via the multiple trenched source-body contacts 214. Furthermore, a p+ body contact region 221 is formed surrounding at least bottom of each the trenched source-body contact 214 to reduce the contact resistance between the tungsten plugs 215 and the p body region 208. As shown in dashed brace, each the P second doped column region 207 and the adjacent N sub-doped column region 206' constitute the P/N charge balance area. In the termination area, a N third doped column region 236 and a P fourth doped column region 237 near a deep trench 234 filled with the thick dielectric layer 205 having a void 230, constitute a second type charge balance area, wherein the N third doped column region 236 has about half column width of the N first doped column region 206 and the fourth doped column region 237 has about same column width as the second doped column region 236 in the unit cell. Therefore, there is no need to have multiple guard rings in the termination area as in the prior art. Moreover, top surface of the void 230 in FIG. 2A is sealed with the thick dielectric layer 205. Besides, an n+ channel stop region 222 is formed near the top surface of the N- epitaxial layer 201 with a trenched termination contact 223 penetrating through the contact interlayer 212, the n+ channel stop region 222 and into the N- epitaxial layer 201, wherein the trenched termination contact 223 has a same filling material with the trenched source-body contact 214 and is connected to an equal potential ring (EPR, the same hereinafter) metal 224. A p+ body contact region 221' is formed surrounding at least bottom of the trenched termination contact 223 to reduce the contact resistance. In this preferred embodiment, all the contact metal plugs can be implemented by using a tungsten plug padded by a barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN. Therefore, the termination area according to the present invention is about 20 um in length, shortening termination length to about one tenth compared with the prior art.

FIG. 2B shows a cross-sectional view of another preferred super junction trench MOSFET 200' according to the present invention which has a similar structure as the super-junction trench MOSFET 200 in FIG. 2A except that in FIG. 2B, there is no EPR metal connected with the trenched termination contact 223' in the termination area.

FIG. 2C shows a cross-sectional view of another preferred super-junction trench MOSFET 200'' according to the present invention which has a similar structure as the super-junction trench MOSFET 200 in FIG. 2A except that in FIG. 2C, the super-junction trench MOSFET 200'' further comprises a passivation layer 260 covering a whole top surface of the termination area including a portion of a top surface of source metal 213'' near the termination area.

FIG. 3A shows a cross-sectional view of another preferred super-junction trench MOSFET 300 according to the present invention which has a similar structure as the super-junction trench MOSFET 200 in FIG. 2A except that in FIG. 3A, the void inside the deep trench 334 in the termination area is opened up in air. Moreover, the EPR metal extends from the channel stop area toward active area and stop before the void.

FIG. 3B shows a cross-sectional view of another preferred super junction trench MOSFET 300' according to the present

invention which has a similar structure as the super-junction trench MOSFET **300** in FIG. 3A except that in FIG. 3B, the super junction trench MOSFET **300'** further comprises a passivation layer **360** covering above the void inside the deep trench **334'** in the termination area.

FIGS. 4A to 4K are a serial of exemplary steps that are performed to form the inventive super junction trench MOSFET **200** in FIG. 2A. In FIG. 4A, an N- epitaxial layer **201** is grown on an N+ substrate **202**, wherein the N+ substrate **202** has a higher doping concentration than the N- epitaxial layer **201**, and shares a common interface with the N- epitaxial layer **201**. Next, a hard mask **270**, which can be implemented by using an oxide layer, is formed covering a top surface of the N- epitaxial layer **201**. Then, after a trench mask (not shown) is applied onto the hard mask **270**, deep trenches **204'** and **234'** is etched through the hard mask **270** and into the N- epitaxial layer **201** by successively dry oxide etch and dry silicon etch.

In FIG. 4B, an isotropic dry silicon etch in down stream plasma is carried out to eliminate the plasma damage introduced during opening the deep trenches **204'** and **234'** and to form the deep trenches **204** and **234**. The hard mask **270** is still remained to block sequential angle ion implantations into the top surface of the N- epitaxial layer **201**.

In FIG. 4C, a pad oxide **271** of about 100 angstroms in thickness is grown along inner surfaces of the deep trenches **204** and **234**. Then, an angle ion implantation of Phosphorus dopant followed by a Phosphorus dopant drive-in step is carried out to form an N first doped column region **206** consist of two N sub-doped column regions **206'** in a mesa between sidewalls of the deep trenches **204** and **234**.

In FIG. 4D, another angle ion implantation of Boron dopant is carried out and followed by a Boron dopant drive-in step to form a pair of P second doped column regions **207** with column shape adjacent to the sidewalls of the deep trenches **204** and **234**, in parallel with and surrounding the N first doped column region **206**.

In termination areas of FIGS. 4C and 4D, an N third doped column **236** and a P fourth doped column **237** is simultaneously formed with the N first doped column **206** and the P second doped column, respectively.

In FIG. 4E, the hard mask **270** (as shown in FIG. 4D) and the pad oxide **271** (as shown in FIG. 4D) are removed away. A dielectric material **205**, for example tetra ethyl ortho silicate (TEOS, the same hereinafter) is formed filling the deep trenches **204** and **234** with a buried void inside the dielectric material **205** and followed by an annealing process. Then, etching back or chemical mechanical polishing (CMP, the same hereinafter) the dielectric material **205** from the top surface of the N- epitaxial layer **201**.

In FIG. 4F, a pad oxide layer **273** is formed on a top surface of the whole device structure in FIG. 4E. Then by applying a p body mask **274**, p body ion implantation and diffusion are successively carried out to form a p body region **208** extending between the deep trenches **204** and **234** and near the top surface of the N- epitaxial layer **201**. After that, the p body mask **274** is removed.

In FIG. 4G, after applying a gate trench mask (not shown), a plurality of gate trenches **209** are etched into the N first doped column region **206**. Afterwards, a sacrificial oxide (not shown) is grown and then removed to eliminate the plasma damage introduced during opening the gate trenches **209**.

In FIG. 4H, a gate oxide layer **211** is grown along inner surfaces of the gate trenches **209**. Then, a doped poly-silicon layer is deposited to fill the gate trenches **209**, and then is etched back by CMP or plasma etch to serve as gate electrodes **210**.

In FIG. 4I, by applying a source mask **277**, an ion implantation of n type dopant and a diffusion step are carried out to form n+ source regions **216** near a top surface of the p body region **208** in active area, and an n+ channel stop region **222** near the top surface of the N- epitaxial layer **201** in termination area.

In FIG. 4J, an insulation layer is deposited onto a whole top surface of the device structure to serve as a contact interlayer **212**. Then, after applying a contact mask (not shown) onto the contact interlayer **212**, a plurality of contact holes **278** and **278'** are formed by successively dry oxide etch and dry silicon etch. After penetrating through the contact interlayer **212**, the contact holes **278** are further penetrating through the n+ source regions **216** and extending into the p body region **208** in the mesa, the contact hole **278'** is extending into the N- epitaxial layer **201**. Next, a BF₂ ion implantation is performed and followed by a step of RTA (rapid thermal annealing) process to form a plurality of p+ body contact regions **221** and p+ body contact region **221'** respectively surrounding at least bottoms of the contact holes **278** and **278'**.

In FIG. 4K, a barrier metal layer Ti/TiN or Co/TiN or Ta/TiN is deposited on sidewalls and bottoms of all the contact holes. Then, a tungsten material layer is deposited onto the barrier metal layer, wherein the tungsten material layer and the barrier metal layer are then etched back to form: contact metal plugs **215** for trenced source-body contacts **214** and contact metal plug **215'** for trenced termination contact **223**. Then, a metal layer of Al alloys or Cu padded by a resistance-reduction layer Ti or Ti/TiN underneath is deposited onto the contact interlayer **212** and followed by a metal etching process by employing a metal mask (not shown) to form a source metal **213** and an EPR metal **224**.

FIGS. 5A and 5B show processing steps for forming the opened up void of the inventive super-junction trench MOSFET **300** in FIG. 3A. After formation of trenced source-body contacts **314** and trenced termination contact **323**, a metal layer of Al alloys or Cu padded by a resistance-reduction layer Ti or Ti/TiN underneath is deposited onto the contact interlayer **312** and followed by a metal etching process by employing a metal mask (not shown) to form a source metal **313** and an EPR metal **324**. Then in FIG. 5B, a dry oxide etch is performed to open up the void inside the deep trench **334** in the termination area by removing oxide in an upper portion of the deep trench **334**.

FIG. 6 is a top view of super-junction trench MOSFETs with square closed cell layout. Closed gate trenches **601** surround a deep trench **602** in each unit cell, wherein the deep trench **602** has square shape. Trenced source-body contacts **603** are disposed between the closed gate trenches **601** and the deep trench **602** in each the unit cell, wherein the trenced source-body contacts **603** have square shape. In some embodiments, the deep trench **602** has rectangular, circle or hexagon shape as an alternative. Trenced source-body contacts **603'** are disposed between the adjacent closed gate trenches **601**.

FIG. 7 is a cross-sectional view of A1-A2 in FIG. 6. N-channel super-junction trench MOSFET **700** comprises a plurality of unit cells with each comprising a plurality of deep trenches **704** formed starting from a top surface of an N- epitaxial layer and vertically down extending into the N+ substrate **702**. A mesa is therefore formed between every two adjacent of the deep trenches **704** in each unit cell wherein an N first doped column region **706** consist of two N sub-doped column regions **706'** each having half column width of the N first doped column region **706** is formed. Adjacent to sidewalls of the deep trenches **704**, a pair of P second doped column regions **707** is formed in the mesa and in parallel

surrounding with the N first doped column region **706**. A first type charge balance area comprising two P/N charge balance areas is formed in the mesa area between the adjacent deep trenches. The N first doped column region **706** and the P second doped column regions **707** all have column bottoms above trench bottoms of the deep trenches **704**. Onto a top surface of the N first doped column region **706** and the P second doped column regions **707**, a p body region **708** is formed between in the mesa extending between every two adjacent of the deep trenches **704**. A pair of gate trenches **709** is penetrating through the p body region **708** further extending into the N first doped column region **706** in each unit cell. In some preferred embodiments, there is only one gate trench penetrating through the p body region further extending into the N first doped column region in each unit cell as an alternative. In each the mesa, multiple trenched source-body contacts **703** with each filled with a tungsten plug padded by a barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN are formed between the deep trench **704** and the gate trench **709** in each unit cell, and trenched source-body contact **703'** filled with the tungsten plug padded by the barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN are formed between the adjacent gate trench **709**. Therefore, the p body region **708** and the n+ source region **716** are connected to the source metal **713** via the multiple trenched source-body contacts **703** and **703'**. Furthermore, a p+ body contact region **721** is formed surrounding at least bottom of each the trenched source-body contact **703** and **703'** to reduce the contact resistance between the tungsten plugs and the p body region **708**.

FIG. **8** shows super-junction trench MOSFETs with rectangular closed cells in single orientation layout, which has a similar structure as the super-junction trench MOSFETs in FIG. **6** except that in FIG. **8**, the deep trench **802** and the trenched source-body contacts **803** has rectangular shape.

FIG. **9** shows super-junction trench MOSFETs with rectangular closed cells in multiple orientations layout, which has a similar structure as the super-junction trench MOSFETs in FIG. **8** except that in FIG. **9**, the layout of the deep trenches **902** have multiple orientations, for example, in horizontal direction and in vertical direction.

FIG. **10** is a top view of super-junction trench MOSFETs with square closed cell layout having shielded gate **1005**. Closed gate trenches **1001** surround a deep trench **1002** in each unit cell, wherein the shielded gate **1005** is formed within the deep trench **1002**. The shielded gate **1005** and the deep trench **1002** have square shape. Trenched shielded gate contact **1006** is disposed in the shielded gate **1005** in each the unit cell, wherein the trenched shielded gate contact **1006** has square shape. Trenched source-body contacts **1003** are disposed between the closed gate trenches **1001** and the deep trench **1002** in each the unit cell, wherein the trenched source-body contacts **1003** have square shape. In some embodiments, the deep trench **1002** has rectangular, circle or hexagon shape as an alternative. Trenched source-body contacts **1003'** are disposed between the adjacent closed gate trenches **1001**.

FIG. **11** is a cross-sectional view of A1-A2 in FIG. **10**. N-channel super junction trench MOSFET **1100** comprises a plurality of unit cells with each comprising a plurality of deep trenches **1104** formed starting from a top surface of an N-epitaxial layer and vertically down extending into the N+ substrate **1102**, wherein shielded gate **1180** is formed within the deep trench **1104** and surrounded with a dielectric material **1181**. A mesa is therefore formed between every two adjacent of the deep trenches **1104** in each unit cell wherein an P first doped column region **1106** consist of two P sub-doped column regions **1106'** each having half column width

of the P first doped column region **1106** is formed. Adjacent to sidewalls of the deep trenches **1104**, a pair of N second doped column regions **1107** is formed in the mesa and in parallel surrounding with the P first doped column region **1106**. A first type charge balance area comprising two N/P charge balance areas is formed in the mesa area between the adjacent deep trenches **1104**. The P first doped column region **1106** and the N second doped column regions **1107** all have column bottoms above trench bottoms of the deep trenches **1104**. Onto a top surface of the P first doped column region **1106** and the N second doped column regions **1107**, a p body region **1108** is formed between in the mesa extending between every two adjacent of the deep trenches **1104**. A pair of gate trenches **1109** filled with doped poly-silicon layer padded by a gate oxide layer having thickness thinner than the dielectric material **1181** filled into the deep trench **1104**, penetrating through the p body region **1108** further extending into the P first doped column region **1106** in each unit cell, wherein the deep trenches **1104** have deeper trench depth than the gate trenches **1109**. In some preferred embodiments, there is only one gate trench penetrating through the p body region further extending into the N second doped column region in each unit cell as an alternative. In each the mesa, multiple trenched source-body contacts **1103** with each filled with a tungsten plug padded by a barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN are formed between the deep trench **1104** and the gate trench **1109** in each the unit cell, and trenched source-body contact **1103'** filled with the tungsten plug padded by the barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN are formed between the adjacent gate trenches **1109**. Therefore, the p body region **1108** and n+ source region **1116** are connected to the source metal **1113** via the multiple trenched source-body contacts **1103** and **1103'**, while the shielded gate **1180** is connected to the source metal **1113** via the trenched shielded gate contact **1190** which filled with the tungsten plug padded by the barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN. Furthermore, a p+ body contact region **1121** is formed surrounding at least bottom of each the trenched source-body contact **703** and **703'** to reduce the contact resistance between the tungsten plugs and the p body region **1108**.

FIG. **12** shows super-junction trench MOSFETs with rectangular closed cells having shielded gate in single orientation layout, which has a similar structure as the super junction trench MOSFETs in FIG. **10** except that in FIG. **12**, the deep trenches **1202**, the trenched source-body contacts **1203**, the shielded gates **1205** and the trenched shielded gate contacts **1206** have rectangular shape.

FIG. **13** shows super-junction trench MOSFETs with rectangular closed cells having shielded gate in multiple orientations layout, which has a similar structure as the super-junction trench MOSFETs in FIG. **12** except that in FIG. **13**, the layout of the deep trenches **1302** have multiple orientations, for example, in horizontal direction and in vertical direction.

Although the present invention has been described in terms of the presently preferred embodiments, it is to be understood that such disclosure is not to be interpreted as limiting. Various alternations and modifications will no doubt become apparent to those skilled in the art after reading the above disclosure. Accordingly, it is intended that the appended claims be interpreted as covering all alternations and modifications as fall within the true spirit and scope of the invention.

What is claimed is:

1. A super-junction trench MOSFET comprising a plurality of unit cells with each unit cell in an active area comprising:
 - a at least one gate trench surrounding a deep trench as a closed cell shape wherein a shielded gate is formed within said deep trench;

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trenched source-body contacts disposed at least between said gate trench and said deep trench;
 a substrate of a first conductivity type;
 an epitaxial layer of said first conductivity type grown on said substrate, said epitaxial layer having a lower doping concentration than said substrate;
 said deep trench having deeper trench depth than said gate trench;
 said shielded gate formed within said deep trench and surrounded by a dielectric material;
 a first doped column region of a second conductivity type with a second column shape between two adjacent of said deep trench;
 a pair of second doped column regions of said first conductivity type with a column shape adjacent to sidewalls of said deep trench formed in parallel with and surrounding said first doped column region to form a charge balance area in connection with said first doped column region;
 a body region of said second conductivity type, covering a top surface of said first and second doped column regions, extending between said deep trenches;
 said gate trench filled with a doped poly-silicon layer padded by a gate oxide layer, starting from the top surface of said epitaxial layer and penetrating down through said body region and extending into said pair of second doped column regions;
 said trenched source-body contacts with each filled with a contact metal plug extending into said body region;

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a source region of said first conductivity type surrounded an upper portion of each said gate trench, extending between the upper portion of each said gate trench and sidewalls of adjacent trenched source-body contacts; and
 a source metal connected with said shielded gate and said source region.
 2. The super-junction trench MOSFET of claim 1 wherein said gate oxide has a thickness thinner than said dielectric material filled into said deep trench.
 3. The super-junction trench MOSFET of claim 1 wherein said deep trench has a square shape.
 4. The super-junction trench MOSFET of claim 1 wherein said deep trench has a circle shape.
 5. The super-junction trench MOSFET of claim 1 wherein said deep trench has a hexagon shape.
 6. The super-junction trench MOSFET of claim 1 wherein said deep trench has a rectangular shape.
 7. The super-junction trench MOSFET of claim 1 further comprising a body contact region of said second conductivity type surrounded at least bottom of each of said trenched source-body contacts, wherein said body contact region has a higher doping concentration than said body region.
 8. The super-junction trench MOSFET of claim 1, wherein said contact metal plug is a tungsten plug padded by a barrier metal layer of Ti/TiN or Co/TiN or Ta/TiN.

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